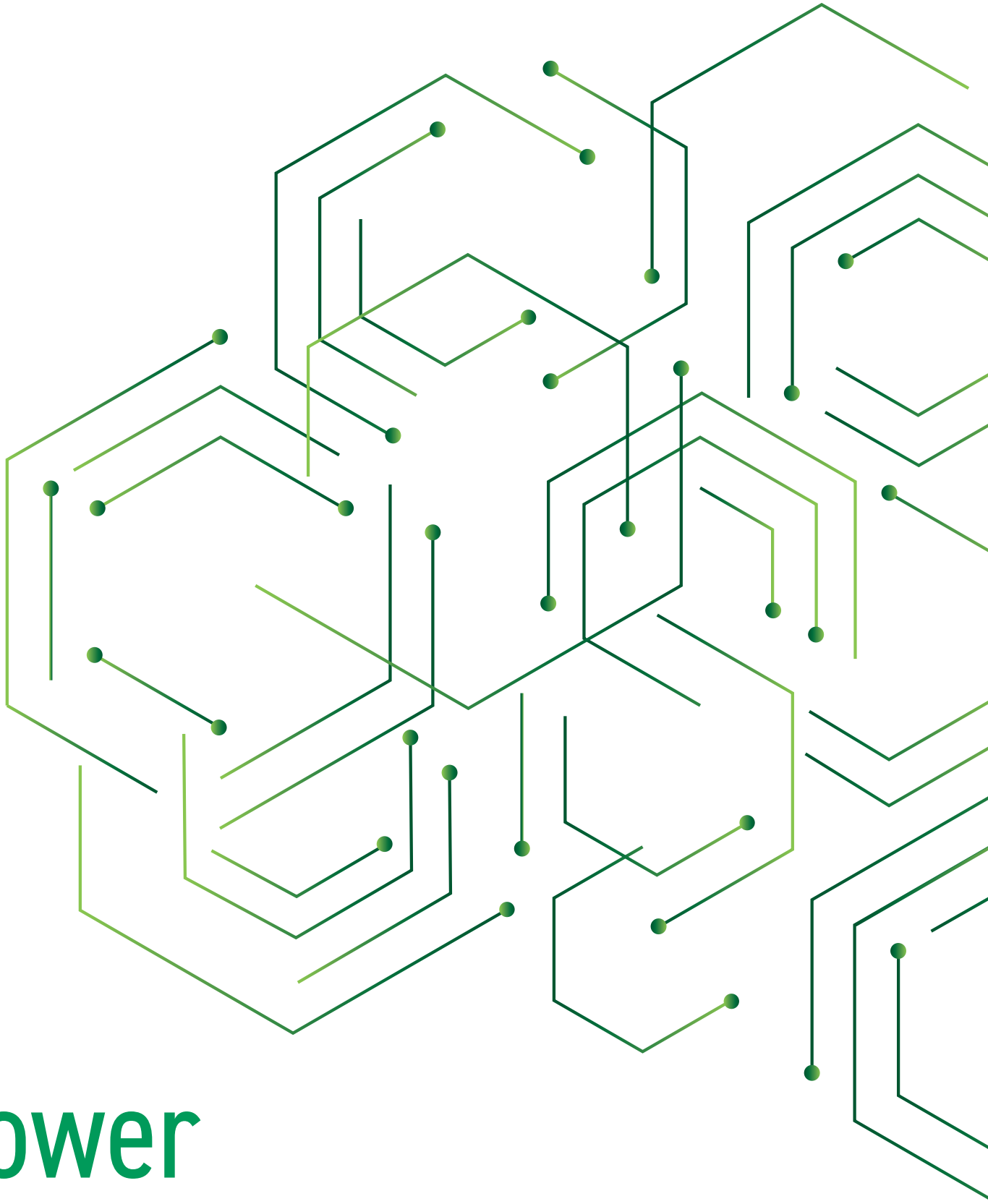
MITSUBISHI ELECTRIC

Changes for the Better

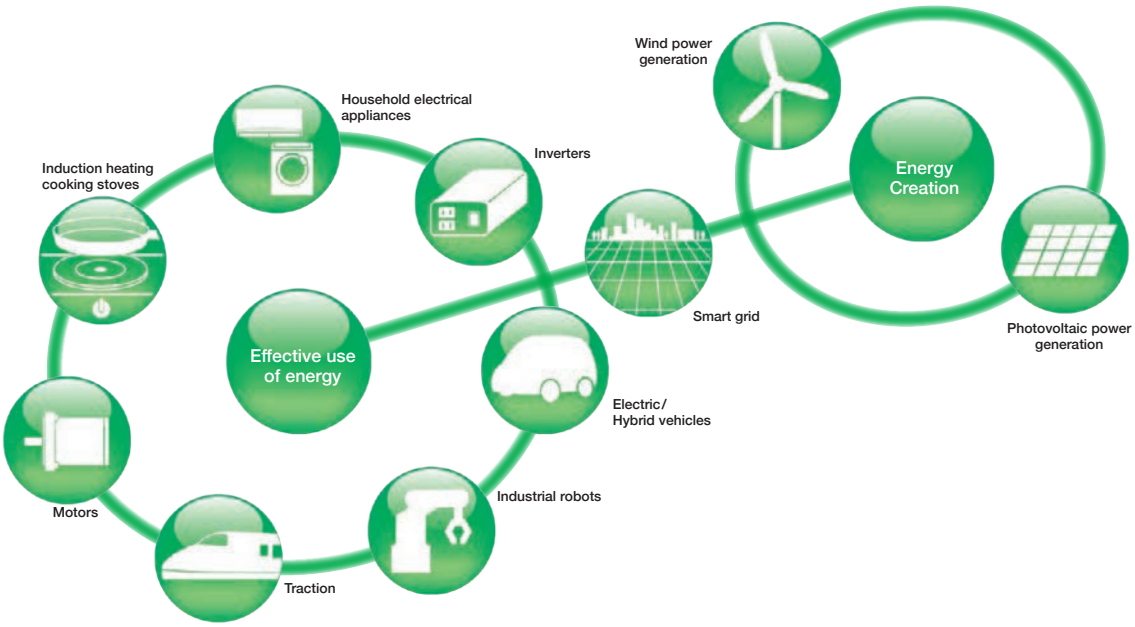
POWER DEVICES

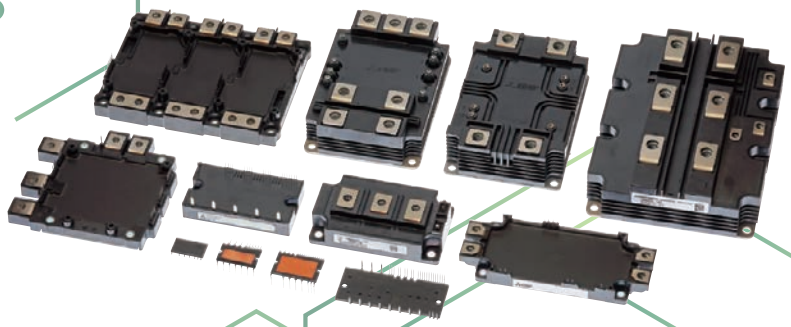


Power Devices

Innovative Power Devices for a Sustainable Future

Mitsubishi Electric power modules are at the forefront of the latest energy innovations that seek to solve global environmental issues while creating a more affluent and comfortable society for all. Some of these innovations are photovoltaic (PV) and wind power generation from renewable energy sources, smart grids realizing efficient supply of power, hybrid/electric vehicles (HVs/EVs) that take the next step in reducing carbon emissions and fuel consumption, and home appliances that achieve ground-breaking energy savings. Whether in appliances, railcars, EVs or industrial systems, our power modules are key elements in changing the way energy is used.





Index

Product	Page	Connection						Rated voltage	Rated current	Main Application
		IGBT Module	Intelligent Power Module	MOSFET Module	Diode Module	Discrete Diode	Discrete MOSFET			
SiC Power Modules	5-11	✓ (Hybrid)	✓	✓				600V 1200V 1700V 3300V	15A-30A 75A-1200A 300A,1200A 375A-750A	Home Appliance Industrial equipment Traction
SiC-MOSFET	12						✓	1200V	38A-95A	Home Appliance Industrial equipment xEV
SiC-SBD	13					✓		600V 1200V	20A 10A,20A	Home Appliance Industrial equipment xEV
SOPIPM	14		✓					600V	2A	Home Appliance
DIPIPM	14-19		✓					600V 1200V	5A-75A 5A-100A	Home Appliance
IPM	20-24		✓					600V 650V 1200V	50A-800A 50A-450A 25A-450A	Industrial equipment
IGBT Modules	25-35	✓						600V 650V 1200V 1700V	75A-600A 50A-600A 35A-1400A 75A-1200A	Industrial equipment
HVIGBT Modules	36-40	✓						1700V 2500V 3300V 4500V 6500V	600A-2400A 400A-1200A 400A-1800A 450A-1500A 200A-1000A	Traction High Power
HVDIODE Modules	41-42				✓			1700V 3300V 4500V 6500V	1200A-1800A 400A-1500A 300A-1500A 200A-1000A	Traction High Power
MOSFET Modules	43			✓				75V 100V 150V	100A-300A	Industrial equipment
Power Modules for xEV*1	44-45	✓						650V	300A-700A	xEV

*1 EV: Electric Vehicle

*2 SOPIPM,DIPIPM,SLIMDIP,DIPIPM+,DIPPFC,CSTBT are trademarks of Mitsubishi Electric

Development of Mitsubishi Electric SiC Power Devices and Power Electronics Equipment Incorporating Them

Mitsubishi Electric began developing SiC as a new material in the early 1990s. Pursuing special characteristics, we succeeded in developing various elemental technologies.
In 2010, we commercialized the first air conditioner in the world equipped with a SiC power device.
Furthermore, substantial energy-saving effects have been achieved for traction and FA machinery.
We will continue to provide competitive SiC power modules with advanced development and achievements from now on.

Early 1990s

Developed new material, silicon-carbide (SiC) power semiconductor, maintaining a lead over other companies

2000s

Developed various elemental technologies

2006

January 2006
Successfully developed SiC inverter for driving motor rated at 3.7kW

2009

February 2009
Verified 11kW SiC inverter, world's highest value*1 with approx. 70% reduction in power loss

November 2009
Verified 20kW SiC inverter, world's highest value*1 with approx. 90% reduction in power loss

2010

January 2010
Developed large-capacity power module equipped with SiC diode

October 2010
Launched "Kirigamine" inverter air conditioner

2011

January 2011
Verified highest power conversion efficiency*1 for solar power generation system power conditioner (domestic industry)*2

October 2011
Commercialized SiC inverter for use in railcars

2012

March 2012
Developed motor system with built-in SiC inverter

September 2012
Verified built-in main circuit system for railcars

July 2012
Began shipping samples of hybrid SiC

December 2012
Launched CNC drive unit equipped with SiC power module

2013

February 2013
Developed SiC for application in elevator control systems

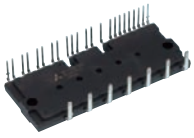
March 2013
Delivered auxiliary power supply systems for railcars

2014

February 2014
Developed EV motor drive system with built-in SiC inverter

May 2014
Began shipping samples of hybrid SiC power modules for high-frequency switching applications

November 2014
Launched Large Hybrid SiC DIPIPM™ for PV Applications



Development of these modules and applications has been partially supported by Japan's Ministry of Economy, Trade and Industry (METI) and New Energy and Industrial Technology Development Organization (NEDO).

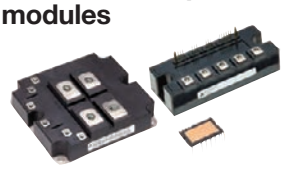
* The year and month listed are based on press releases or information released during the product launch month in Japan.

Contributing to the realization of a low-carbon society and more affluent lifestyles

2013

February 2013
Developed technologies to increase capacities of SiC power modules

May 2013
Launched SiC power modules



December 2013
Launched railcar traction inverter with full SiC power module

2015

January 2015
Launched power conditioner for PV equipped with full SiC-IPM*2

June 2015
Railcar traction system with full SiC power modules installed in Shinkansen bullet trains

2016

April 2016
Launched Super mini Full SiC DIPIPM™

May 2016
Launched room air conditioners with full SiC DIPIPM™ in Japan

October 2016
Launched package air conditioners with full SiC DIPIPM™ in Japan

2017

March 2017
Launched SiC-SBD

March 2017
Develops World's smallest SiC Inverter for HEVs.

September 2017
Develops SiC Power Device with Record Power Efficiency

December 2017
Mitsubishi Electric and the University of Tokyo Quantify Factors for Reducing SiC Power Semiconductor Resistance by Two-Thirds

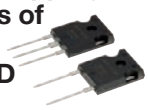
2018

January 2018
New 6.5kV Full-SiC Power Semiconductor Module Achieves World's Highest Power Density

December 2018
Mitsubishi Electric and the University of Tokyo Reveal New Mechanism for Enhancing Reliability of SiC Power Semiconductor Devices

2019

June 2019
Began shipping samples of 1200V SiC-SBD



February 2019
Develops Super Compact Power Unit for Hybrid Electric Vehicle

September 2019
Trench-type SiC-MOSFET with unique electric-field-limiting structure developed

2020

November 2020
Launched 4-terminal SiC-MOSFETs

July 2020
Launched SiC-MOSFET

July 2020
Develops Accurate Circuit Simulation Technology for SiC-MOSFETs

2021

January 2021
Launched Second-generation Full-SiC Power Modules

*1 Researched in press releases by Mitsubishi Electric.
*2 Mitsubishi Electric solar-power generation system discontinued on March 31, 2020.

SiC Power Modules

Data sheet here

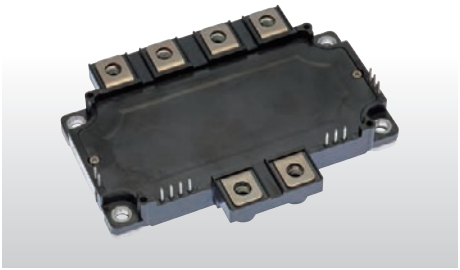
Lineup of SiC Power Modules

Application	Product name	Model	Rating		Connection	States	Page
			Voltages[V]	Current[A]			
Industrial equipment	Full SiC Power Modules	FMF300BXZ-24B	1200	300	4in1	Under development	6
		FMF400BX-24B		400	4in1		
		FMF400BXZ-24B		400	4in1		
		FMF600DXZ-24B		600	2in1		
		FMF800DX-24B		800	2in1		
		FMF800DXZ-24B		800	2in1		
		FMF1200DXZ-24B		1200	2in1		
		FMF300DXZ-34B	1700	300	2in1		
		FMF300E3XZ-34B		300	2in1(Chopper)		
	Full SiC-IPM	PMF75CGA120	1200	75	6in1		7
		PMF75CGAL120					
	Hybrid SiC Power Modules for High-frequency Switching Applications	CMH100DY-24NFH	1200	100	2in1	Commercially available	
		CMH150DY-24NFH		150			
		CMH200DU-24NFH		200			
		CMH300DU-24NFH		300			
		CMH300DX-24NFH		300			
		CMH400DU-24NFH		400			
		CMH600DU-24NFH		600			
		CMH400HC6-24NFM		400	1in1		
Traction inverter HVDC system	Full SiC Power Modules	FMF375DC-66A	3300	375	2in1		8
		FMF750DC-66A		750			
	Hybrid SiC Power Modules	CMH600DC-66X	3300	600			
		CMH1200DC-34S	1700	1200			
Home appliances	Super mini Full SiC DIPIPM	PSF15S92F6	600	15	6in1		9
		PSF25S92F6		25			
	Super mini Hybrid SiC DIPPFC	PSH30L92C6-W	600	30Arms	Three-phase interleaved		
		PSH20L91A6-A		20Arms	Two-phase interleaved		
	Super mini Full SiC DIPPFC	PSF20L91A6-A					

Full-SiC Power Modules for Industrial Equipment

Under development

Contributes to reducing size/weight of industrial-use inverters



Features

- Power loss reduced approx. 70% compared to the conventional product*
- Low-inductance package adopted to deliver full SiC performance
- Contributes to incereasing the output current and downsizing peripheral components by low power loss characteristics of SiC

*Comparison with the same rated value of the conventional 7th Gen. IGBT modules

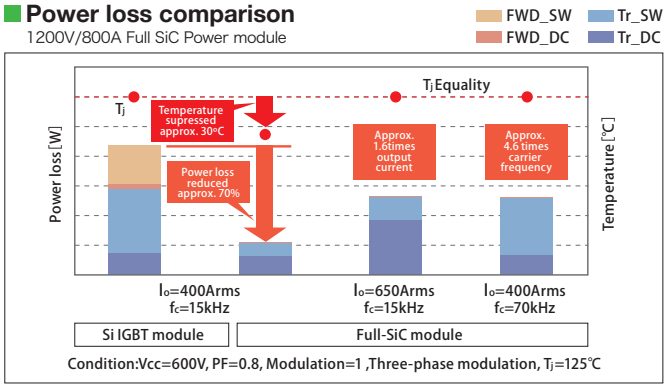
Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
FMF400BX-24B★★	1200V	400A	4 in 1	92.3mm ×121.7mm
FMF800DX-24B★★		800A	2 in 1	

★★:Under development

Power loss comparison

1200V/800A Full SiC Power module



Full-SiC Power Modules for Industrial Equipment (built-in short-circuit protection function)

Under development

Contributes to enhancing the performance of industrial-use inverters thanks to built-in protection function for short circuit

Features

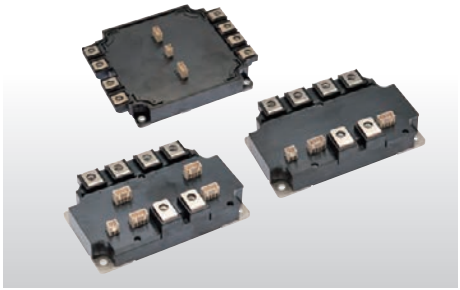
- By using short circuit monitoring circuit in the module it is possible to transfer a short circuit detection signal to the system side
- Power loss reduced approx.70% compared to the conventional product*
- Low- inductance package adopted to deliver full SiC performance

*Comparison with the same rated value of the conventional 7th Gen. IGBT modules

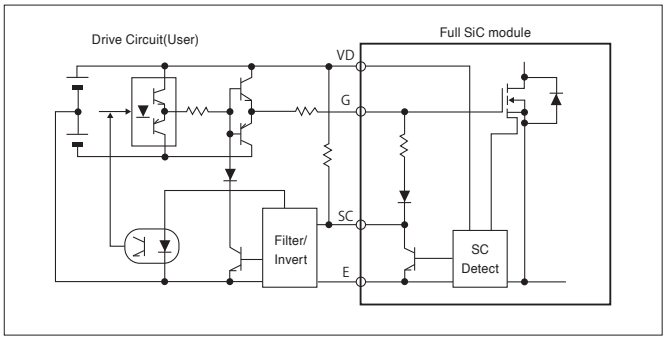
Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
FMF300BXZ-24B★★	1200V	300A	4 in 1	79.6mm×122mm
FMF400BXZ-24B★★		400A	4 in 1	
FMF600DXZ-24B★★		600A	2 in 1	
FMF800DXZ-24B★★		800A	2 in 1	
FMF1200DXZ-24B★★		1200A	2 in 1	152mm×122mm
FMF300DXZ-34B★★	1700V	300A	2 in 1	79.6mm×122mm
FMF300E3XZ-34B★★		300A	2 in 1(Chopper)	

★★:Under development

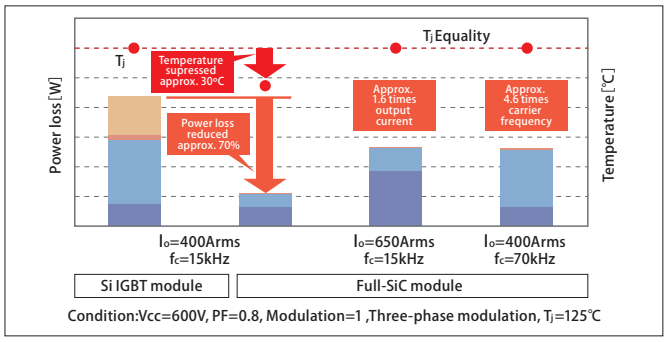


Protection circuit diagram



Power loss comparison

1200V/800A Full SiC Power module



1200V/75A Full SiC-IPM for Industrial Equipment
PMF75CGA120/PMF75CGAL120 Under development

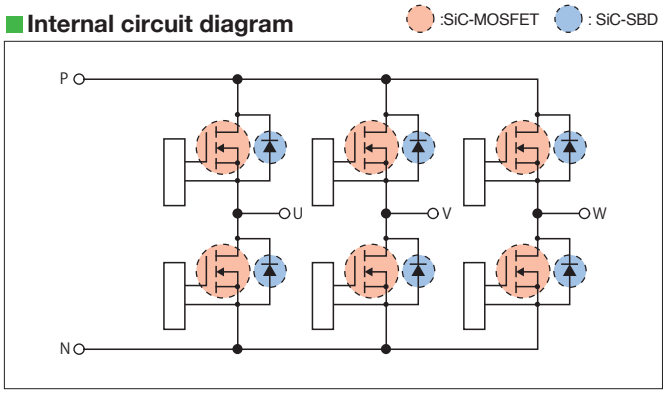
SiC chips(MOSFET and Schottky Barrier Diode) incorporated in an IPM with a built-in drive circuit and protection functions Power loss reduction of approx.70% contributes to improving the performance of industrial equipment

Features

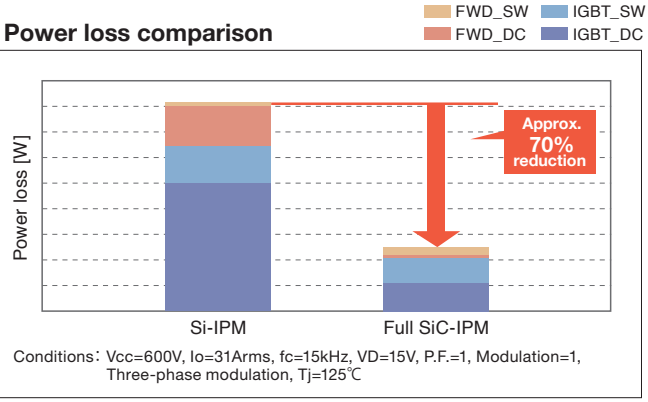
- Realized high performance and low power loss by 2nd. generation SiC-MOSFET and SiC-SBD with current sense and temperature sense
- External size is reduced approx.30% with the conventional Silicon IPM products* of the same rating.
- Available to drive it by the equivalent I/F and power supply circuit with the Silicon IPM products.

* Conventional product: Mitsubishi Electric G1 Series PM75CG1B120

Internal circuit diagram



Power loss comparison



Conditions: Vcc=600V, Io=31Arms, fc=15kHz, VD=15V, P.F.=1, Modulation=1, Three-phase modulation, Tj=125°C

Hybrid SiC Power Modules for High-frequency Switching Applications Commercially available

For optimal operation of power electronics devices that conduct high-frequency switching

Features

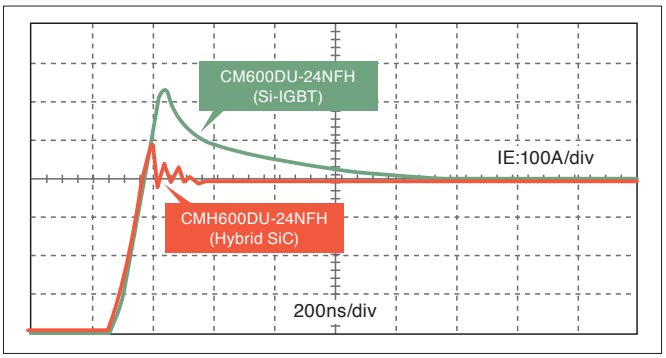
- Power loss reduction of approx. 40% contributes to higher efficiency, smaller size and weight reduction of total system
- Suppresses surge voltage by reducing internal inductance
- Package compatible with the conventional product*

* Conventional product: Mitsubishi Electric NFH Series IGBT Modules

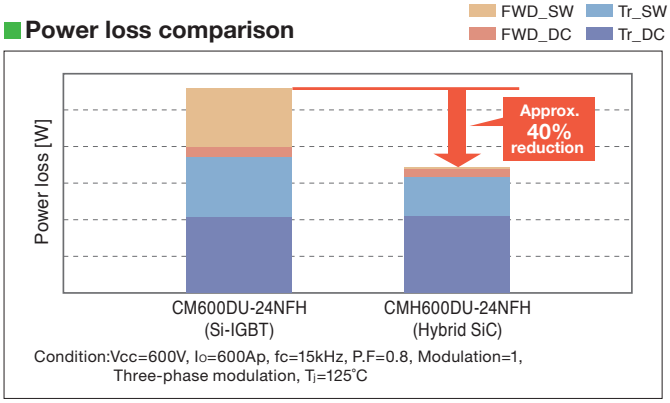
Product lineup

Applications	Model	Rated voltage	Rated current	Circuit configuration	External size (D x W)
Industrial equipment	CMH100DY-24NFH	1200V	100A	2 in 1	48×94mm
	CMH150DY-24NFH		150A		48×94mm
	CMH200DU-24NFH		200A		62×108mm
	CMH300DU-24NFH		300A		62×108mm
	CMH300DX-24NFH		300A		62.5 ×152mm
	CMH400DU-24NFH		400A		80×110mm
	CMH600DU-24NFH		600A		80×110mm
	CMH400HC6-24NFM		400A	1 in 1	62×108mm

Recovery waveform (FWD)



Power loss comparison



Condition:Vcc=600V, Io=600Ap, fc=15kHz, P.F=0.8, Modulation=1, Three-phase modulation, Tj=125°C

3300V Full/Hybrid SiC Power Modules for Traction Inverters and HVDC system
FMF375DC-66A / FMF750DC-66A
CMH600DC-66X Commercially available

Contributes to energy saving and downsizing for inverters in traction motors, DC-power transmitters, large industrial machinery

Features

- Suitable chip set combination for high speed switching
- Reduced power loss compared to the conventional products*
- Low inductance package maximize SiC perfomance

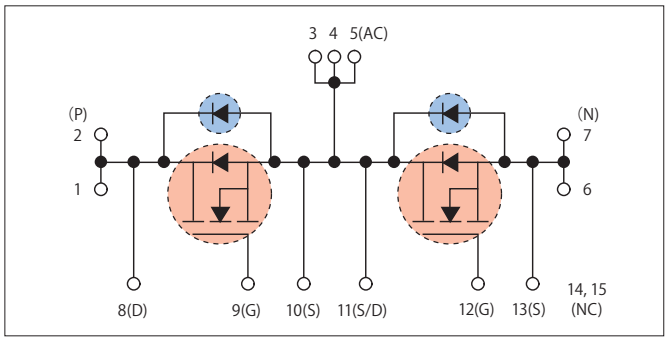
* Si product: Mitsubishi Electric HVIGBT, CM600DC-66X

Product lineup

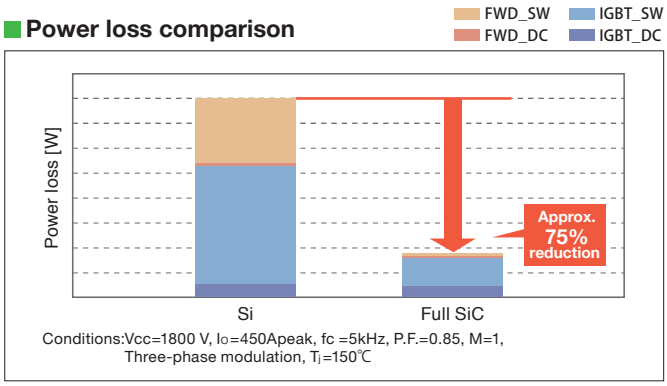
	Model	Rated Voltage	Rated Current	Circuit configuration	External size (D x W)
Full SiC	FMF375DC-66A★	3300V	375A	2 in 1	100 x 140 mm
	FMF750DC-66A		750A		
Hybrid SiC	CMH600DC-66X★		600A		

★:New Product

Internal circuit diagram (e.g. Full SiC) :SiC-MOSFET :SiC-SBD



Power loss comparison



Conditions:Vcc=1800 V, Io=450Apeak, fc =5kHz, P.F.=0.85, M=1, Three-phase modulation, Tj=150℃

1700V/1200A Hybrid SiC Power Modules for Traction Inverters
CMH1200DC-34S Commercially available

High-power/low-loss/highly reliable modules appropriate for use in traction inverters

Features

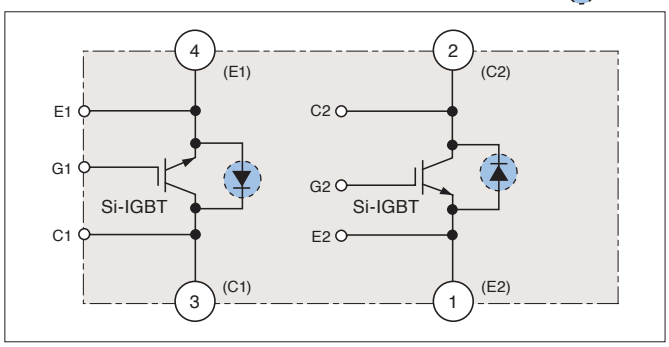
- Power loss reduced approximately 30% compared to the conventional product*
- Highly reliable design appropriate for use in traction
- Package compatible with the conventional product*

* Conventional product: Mitsubishi Electric Power Module CM1200DC-34N

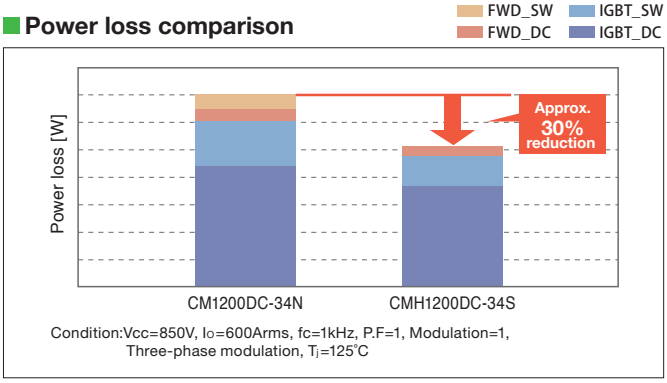
Main specifications

Module	Max.operating temperature		150˚C
	Isolation voltage		4000Vrms
Si-IGBT @150˚C	Collector-emitter saturation voltage		2.3V
	Switching loss 850V/1200V	turn-on	140mJ
		turn-off	390mJ
SiC-SBD @150˚C	Emitter-collector voltage		2.3V
	Capacitive charge		9.0μC

Internal circuit diagram :SiC-SBD



Power loss comparison



Condition:Vcc=850V, Io=600Arms, fc=1kHz, P.F=1, Modulation=1, Three-phase modulation, Tj=125˚C

15A/25A Super mini Full / Hybrid SiC DIPIPM™ for Home Appliances PSF15S92F6-A/PSF25S92F6-A

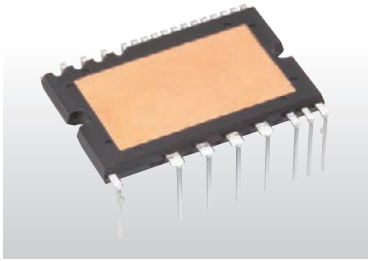
Commercially available

Contributes to extremely high power-efficiency in air conditioners, and easily applicable to industrial equipment

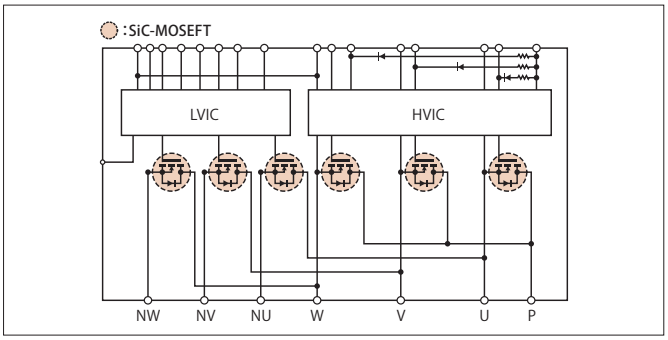
Features

- SiC-MOSFET achieves reduction in ON resistance, power loss reduced approx. 70% compared to conventional product*
- Construct low-noise system by reducing recovery current
- Numerous built-in functions: Bootstrap diode for power supply to drive P-side, temperature information output, etc.
- Unnecessary minus-bias gate drive circuit using original high Vth SiC-MOSFET technology
- As package and pin layout compatibility with conventional products* is ensured, simply replace with this product to improve performance

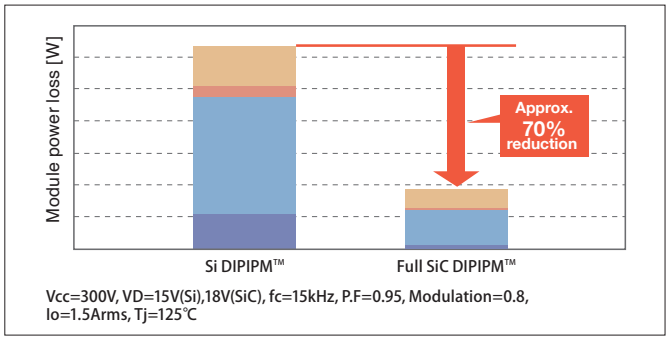
*Conventional product: Mitsubishi Electric Super mini DIPIPM™ Series



Internal block diagram



Power loss comparison



Vcc=300V, VD=15V(Si),18V(SiC), fc=15kHz, P.F=0.95, Modulation=0.8, Io=1.5Arms, Tj=125℃

Super mini Full / Hybrid SiC DIPPFC™ for Home Appliances PSH20L91A6-A / PSF20L91A6-A / PSH30L92C6-W

Commercially available

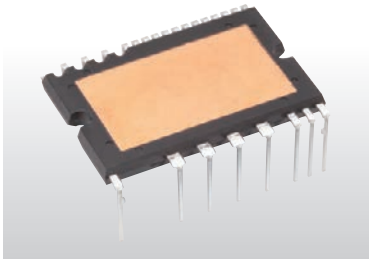
Utilizing SiC enables high-frequency switching and contributes to reducing the size of peripheral components

Features

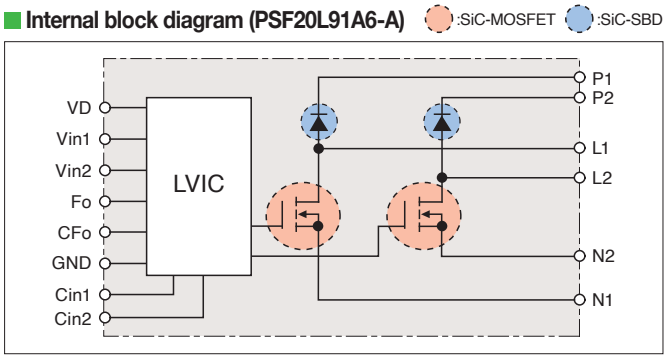
- Incorporating SiC chip in the Super mini package widely used in home appliances
- The SiC chip allows high-frequency switching (up to 40kHz) and contributes to downsizing the reactor, heat sink and other peripheral components
- Adopts the same package as the Super mini DIPIPM™ to eliminate the need for a spacer between the inverter and heat sink, and to facilitate its implementation

Product lineup

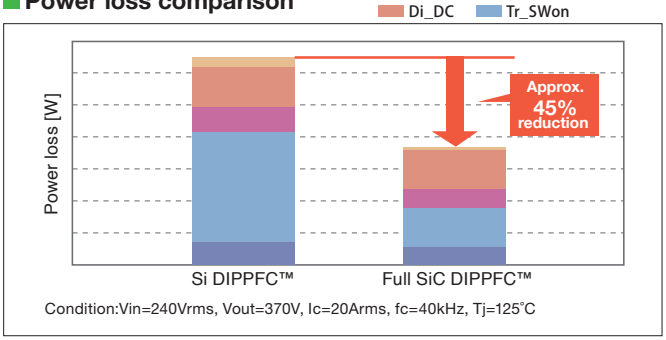
Model	Circuit configuration	Chips
PSH20L91A6-A	2phase Interleaved	Hybrid SiC
PSF20L91A6-A		Full SiC
PSH30L92C6-W	3phase Interleaved	Hybrid SiC



Internal block diagram (PSF20L91A6-A)



Power loss comparison

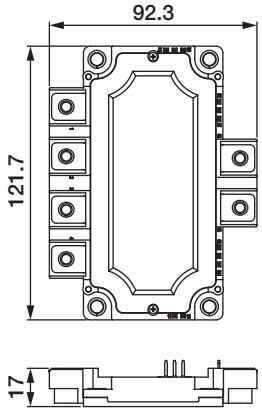


Condition:Vin=240Vrms, Vout=370V, Ic=20Arms, fc=40kHz, Tj=125℃

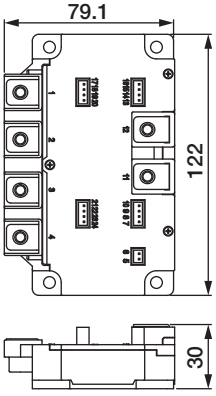
Outline Drawing of SiC Power Modules

Unit:mm

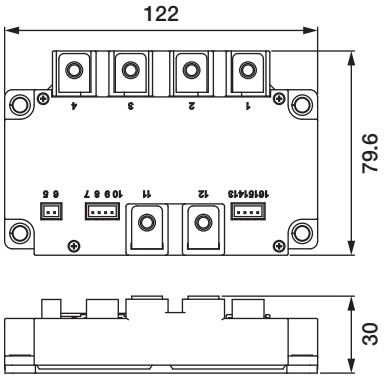
Full SiC Power Modules for Industrial Equipment
FMF400BX-24B,
FMF800DX-24B



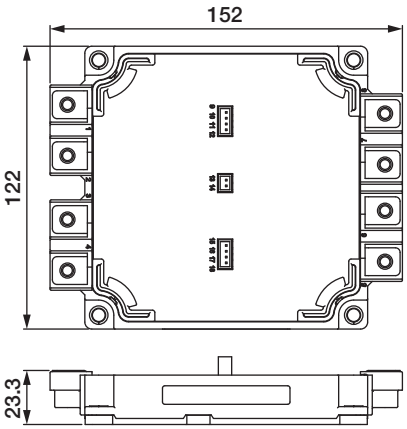
Full SiC Power Modules for Industrial Equipment
FMF300BXZ-24B
FMF400BXZ-24B



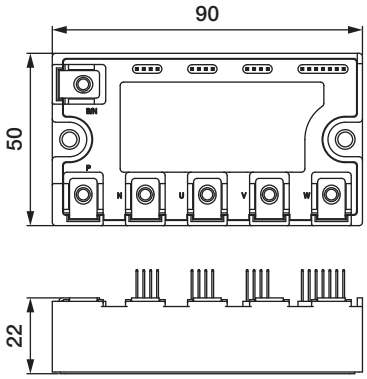
Full SiC Power Modules for Industrial Equipment
FMF600DXZ-24B/FMF800DXZ-24B
FMF300DXZ-34B/FMF300E3XZ-34B



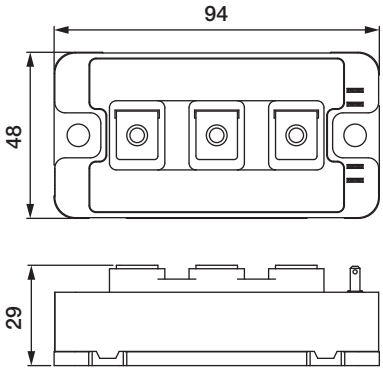
Full SiC Power Modules for Industrial Equipment
FMF1200DXZ-24B



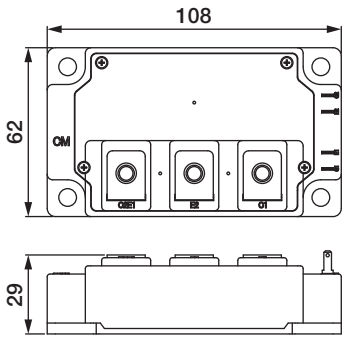
Full SiC IPM for Industrial Equipment
PMF75CGA120
PMF75CGAL120



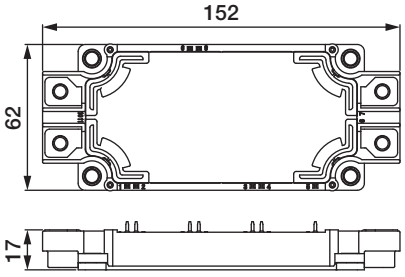
Hybrid SiC Power Modules for High-frequency Switching Applications
CMH100DY-24NFH
CMH150DY-24NFH



Hybrid SiC Power Modules for High-frequency Switching Applications
CMH200DU-24NFH
CMH300DU-24NFH



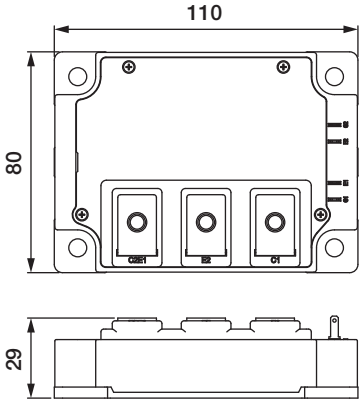
Hybrid SiC Power Modules for High-frequency Switching Applications
CMH300DX-24NFH



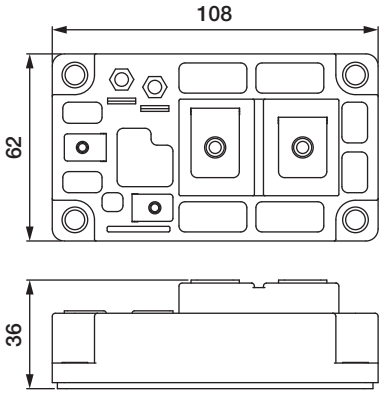
Outline Drawing of SiC Power Modules

Unit:mm

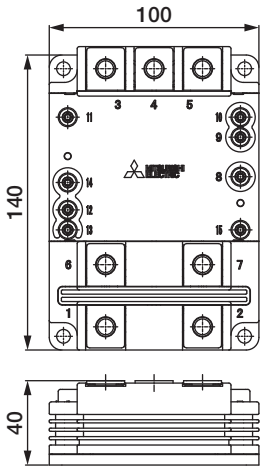
Hybrid SiC Power Modules for High-frequency Switching Applications
CMH400DU-24NFH
CMH600DU-24NFH



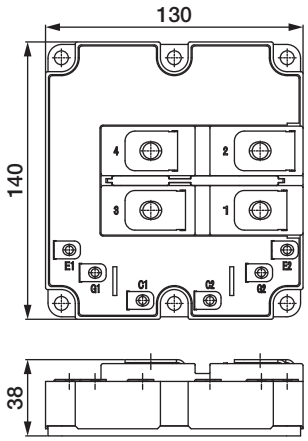
Hybrid SiC Power Modules for High-frequency Switching Applications
CMH400HC6-24NFM



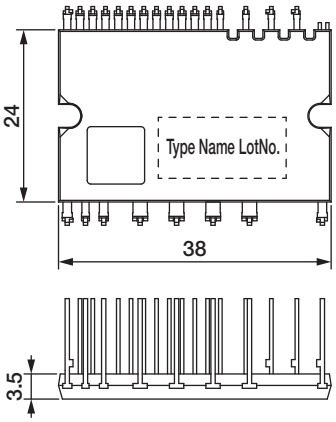
3300V Full/Hybrid SiC Power Modules for Traction Inverters and HVDC system
FMF375DC-66A/FMF750DC-66A
CMH600DC-66X



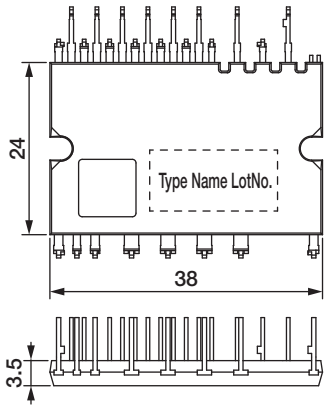
1700V/1200A Hybrid SiC Power Module for Traction Inverters
CMH1200DC-34S



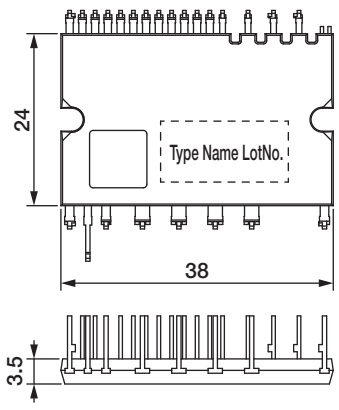
Super mini Full SiC DIPIPM™
PSF15S92F6-A / PSF25S92F6-A
Super mini Full/Hybrid SiC DIPPFC™
PSH20L91A6-A/PSF20L91A6-A
Long



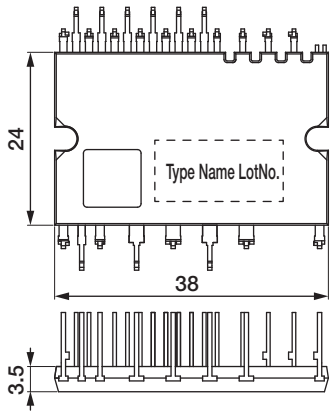
Super mini Full SiC DIPIPM™
PSF15S92F6-C/PSF25S92F6-C
Control side of Zigzag



Super mini Full SiC DIPIPM™
PSF15S92F6/PSF25S92F6
Short



Super mini Hybrid SiC DIPPFC™
PSH30L92C6-W
Both side of Zigzag



SiC-MOSFET for power supply systems
1200V N-series Sample available

Contribute to reducing power loss and the size of power supply systems

Features

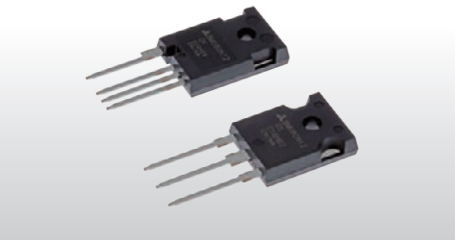
- Junction field effect transistor (JFET) doping technology reduces both switching loss and on-resistance, achieving power loss reduction by approx. 80%* compared to the conventional silicon (Si) products.
- The SiC-MOSFET allows high frequency switching and contributes to downsizing the reactor, heat sink and other peripheral components

* Conventional silicon (Si) product: Mitsubishi Electric 1200V IGBT

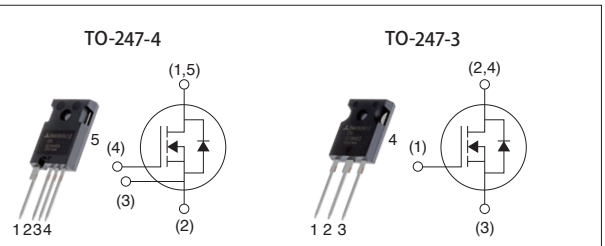
Product lineup

Application	Model	Rating			Package
		Voltage	RDS(on)	Current	
Automotive	BM080N120SJ**	1200V	80mΩ	38A	TO-247-3
	BM080N120KJ**				TO-247-4
	BM040N120SJ**		40mΩ	68A	TO-247-3
	BM040N120KJ**				TO-247-4
	BM022N120SJ**		22mΩ	95A	TO-247-3
	BM022N120KJ**				TO-247-4
Home appliance・Industrial equipment	BM080N120S**	1200V	80mΩ	38A	TO-247-3
	BM080N120K**				TO-247-4
	BM040N120S**		40mΩ	68A	TO-247-3
	BM040N120K**				TO-247-4
	BM022N120S**		22mΩ	95A	TO-247-3
	BM022N120K**				TO-247-4

★★Under development



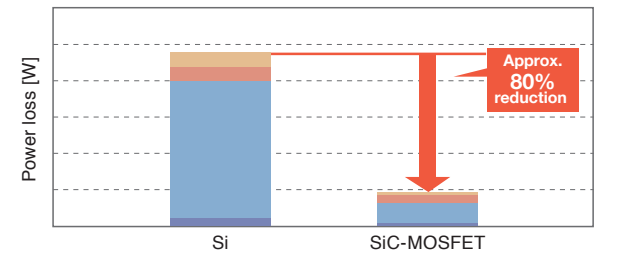
Inner circuit



(1)Drain (2)Source (3)Driver Source (4)Gate (5)Drain

(1)Gate (2)Drain (3)Source (4)Drain

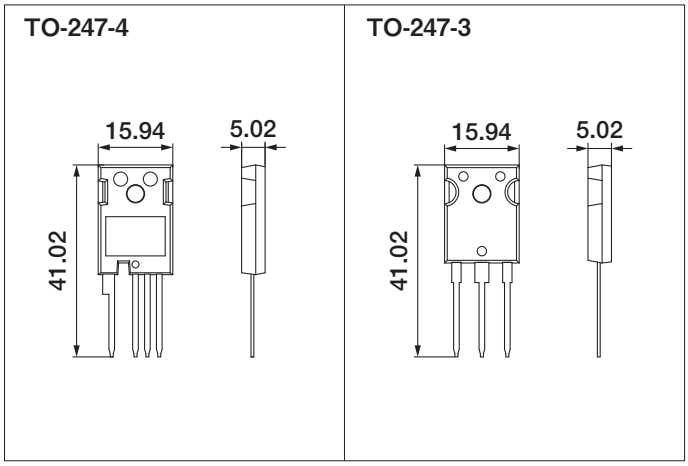
Power loss comparison



Conditions:Vin=230V, Vout=800V, L=0.5mH, fc=150kHz, Iin=15A, Tj=100℃, 3-phase PFC

Outline Drawing of SiC-MOSFET

Unit:mm



SiC-SBD(Schottky Barrier Diode) for power supply systems
600V series 1200V series

Sample available

Contribute to reducing power loss and the size of power supply systems

Features

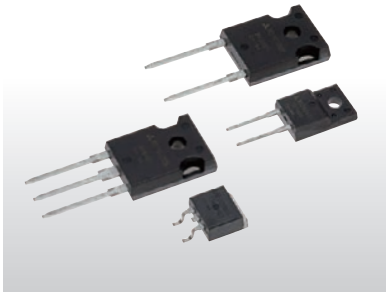
- Power loss is reduced by approx. 21%*1 compared to the conventional silicon (Si) products, contributing to energy conversion.
- The SiC-SBD allows high frequency switching and contributes to downsizing the reactor, heat sink and other peripheral components
- JBS*2 structure allows high forward surge capability and contributes to improving reliability

*1 Conventional Si (Silicon) product: Si diode which is equipped with Mitsubishi Electric DIPPFC™
*2 Junction Barrier Schottky

Product lineup

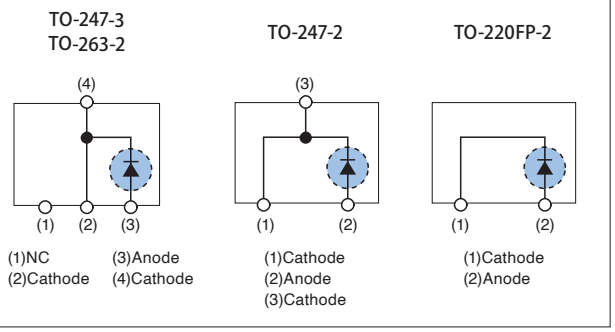
Application	Model	Rated Voltage	Rated Current	Package
Home appliance Industrial equipment	BD20060T	600V	20A	TO-220FP-2
	BD20060A			TO-263-2
	BD20060S★★			TO-247-3
	BD20120S★★	1200V	20A	TO-247-3
	BD20120P★★			TO-247-2
Automotive	BD20120SJ★★			TO-247-3

★★Under development

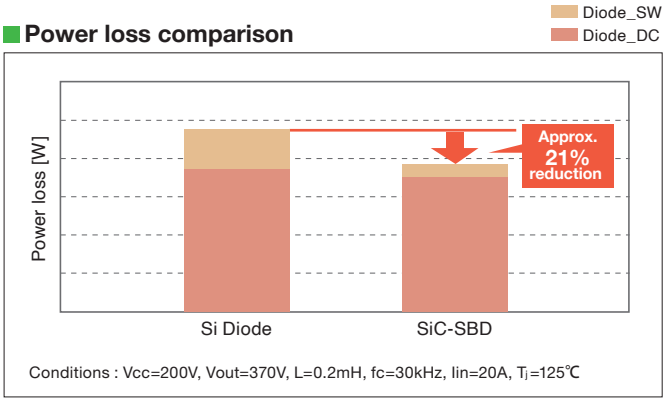


Inner circuit

: SiC-SBD

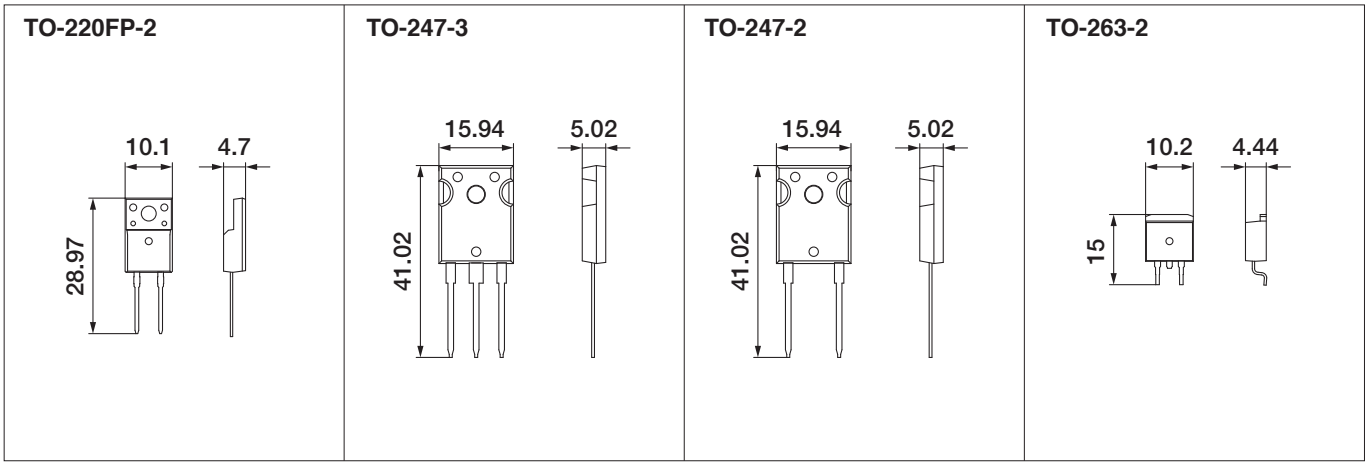


Power loss comparison



Outline Drawing of SiC-SBD

Unit:mm



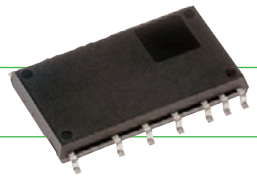
Package, Main Application

Package	Main application
SOPIPM	Fan motor
SLIMDIP	Air conditioner/Fan motor/Washing machine/Refrigerator
Super mini	Air conditioner/Washing machine/Servo/Robot
Mini	Air conditioner/Motion control
Large	Commercial air conditioner/Motion control
DIPIPM+	Commercial air conditioner/Motion control
Large DIPIPM+	Commercial air conditioner/Motion control

Data sheet here

Rated Lineup

New Products



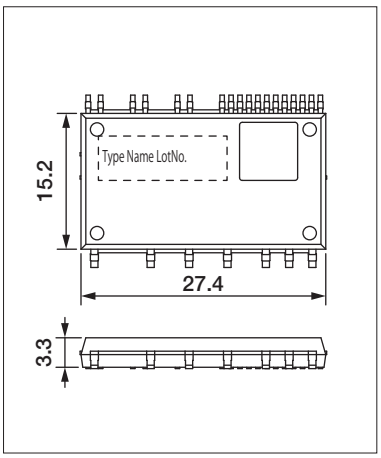
Surface mount package IPM SOPIPM™

A small surface mount package IPM enables easy system design by enough insulation distance and protection function for fan and low-power motor drive applications

<Main Features>
- Optimal pin layout realizes easier PCB wiring design and enables smaller PCB size
- Insulation distance between pins ensured, realizing easier board mounting without coating process
- Newly integrated interlock function in addition to conventional protection features for robust operation
- Installing RC-IGBT*1 simultaneously realizes compact package and low loss performance can go thogether
- Bootstrap diode is integrated for the P-side drive power supply like conventional DIPIPM™ series, reducing the number of peripheral external parts

*1 Reverse-conducting IGBT

Outline Drawing

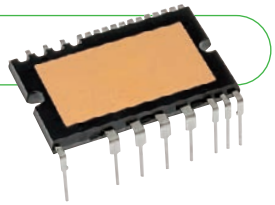


SOPIPM™

Type name	Rated current	Rated voltage	Chips	Protection	Shape
SP2SK	2A	600V	RC-IGBT, HVIC, LVIC, BSD	UV, SC, OT V_{OT}, IL	Surface mount package

[Term] UV : Power supply Under Voltage protection
SC : Short Circuit protection
OT : Over Temperature protection
V_{OT} : Analog Temperature Output
IL : Inter Lock

New Products



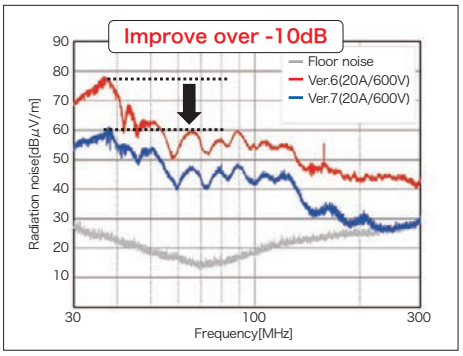
New design with expanded operating temperature range and lower noise contributes to easier system design and reduction in system cost

Super Mini DIPIPM™ Ver.7

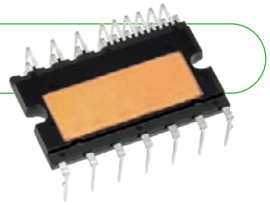
<Main Features>
- New low-noise 7th-generation CSTBT*1 incorporated, keeping same efficiency as DIPIPM Ver.6 Series. System cost reduction for noise suppression parts achieved.
- Maximum junction temperature range expanded to 175°C, supporting instantaneous overcurrent capability at overload operation
- Wider terminal base shape contributes to improved terminal strength and suppresses increase in temperature
- High compatibility for terminal layout, easy to replase from the conventional series

*1 CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

Radiation noise



Featured Products



Expanded line up for SLIMDIP series contributes system cost down for home appliances and fan drive application.

SLIMDIP™ SLIMDIP-S, SLIMDIP-M, SLIMDIP-L, SLIMDIP-W

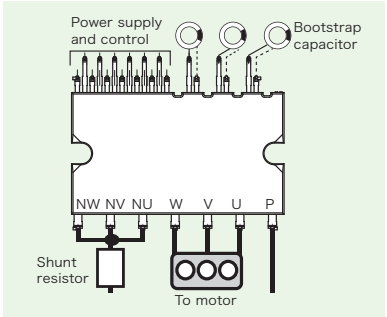
<Main Features>
- RC-IGBT*1 incorporated, reducing package size 30% compared to Super mini DIPIPM
- Maximum case temperature expanded to 115°C, increasing the operating temperature range and leading to easier system design temperature range and leading to easier system design
- Additional terminals for floating supply and built-in bootstrap diodes simplify PCB wiring pattern
- Both V_{OT}*2 and OT*3 functions integrated for temperature protection
- New SLIMDIP-M line-up for washing machine, fans and so on

*1 Reverse conducting IGBT *2 V_{OT}：Analog Temperature Output *3 OT：Over Temperature protection

Product lineup

Type name	Main application
SLIMDIP-S	Fan, refrigerator
SLIMDIP-M	Fan, washing machine
SLIMDIP-L	Air conditioner
SLIMDIP-W	Washing machine, Fan

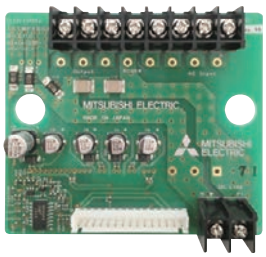
Wiring example



Customer Support

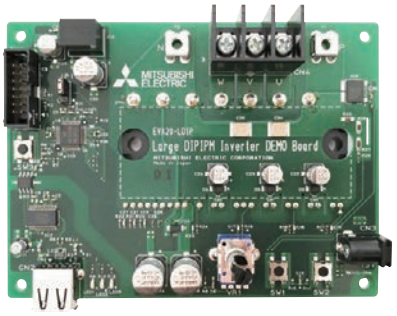
EVA Series evaluation boards for each DIPIPM Series to support system design

For Super mini DIPIPM
EVA11-SDIP



For DIPIPM+
EVA14-DIP+

For SOPIPM
EVA18-SOP



For Large DIPIPM Series
(Microcomputer-embedded demonstration board)
EVA20-LDIP

* For further information, please contact sales office.

Lineup of DIPIPM™

Series Matrix of 600V DIPIPM™

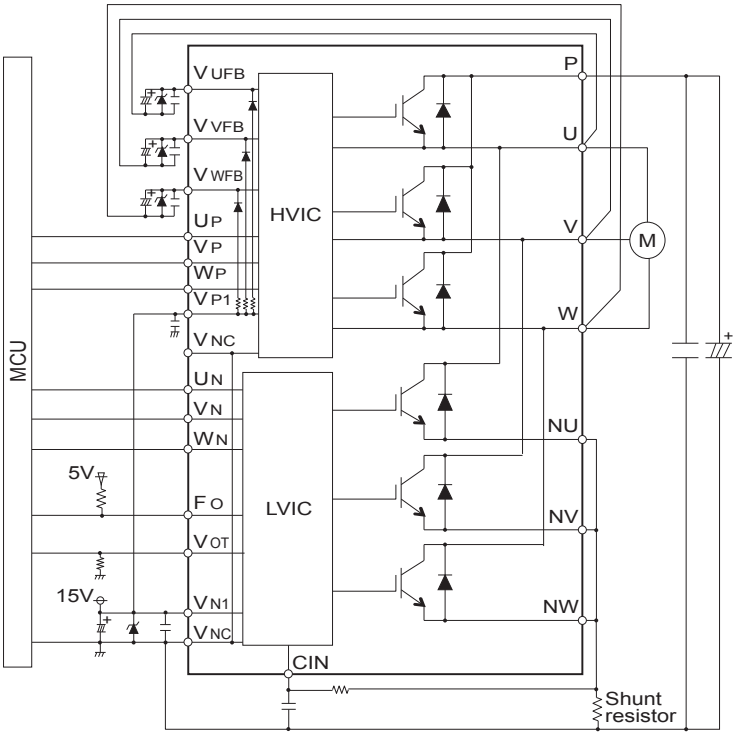
V_{CES}	600V						
Series / I_C	SLIMDIP	Super mini		Mini		Large	DIPIPM+
		Ver.7	Ver.6	Ver.7	–	Ver.6	CIB/CI
5A	SLIMDIP-S		PSS05S92F6-AG PSS05S92E6-AG		PSS05S51F6		
10A	SLIMDIP-M★		PSS10S92F6-AG PSS10S92E6-AG		PSS10S51F6		
15A	SLIMDIP-L SLIMDIP-W	PSS15S93F6-AG★ PSS15S93E6-AG★	PSS15S92F6-AG PSS15S92E6-AG		PSS15S51F6		
20A		PSS20S93F6-AG PSS20S93E6-AG	PSS20S92F6-AG PSS20S92E6-AG	PSS20S73F6	PSS20S51F6 PSS20S71F6		
30A		PSS30S93F6-AG PSS30S93E6-AG	PSS30S92F6-AG PSS30S92E6-AG	PSS30S73F6	PSS30S71F6		
35A			PSS35S92F6-AG PSS35S92E6-AG				
40A		PSS40S93F6-AG PSS40S93E6-AG					
50A				PSS50S73F6	PSS50S71F6	PSS50SA2F6	PSS50MC1F6 PSS50NC1F6*5
75A						PSS75SA2F6	
Chip	RC-IGBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
Protective Function: UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/ N-side/ Brake
Protective Function: SC	N-side	N-side	N-side	N-side	N-side	N-side with sense	N-side
Protective Function: OT	N-side	N-side*1	N-side*1	–	–	–	–
Protective Function: VOT	N-side	N-side*1	N-side*1	N-side	N-side	N-side	N-side
Specifications: Active input	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(5V)
Specifications: Emitter pin of N-side	Open	Open	Open	Open	Open	Open	Open
Specifications: Fault output	N-side(UV,SC,OT)	N-side (UV,SC,OT)	N-side(UV,SC,OT)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
Specifications: Insulation voltage	2000Vrms*2	1500Vrms*2	1500Vrms*2	2500Vrms	2500Vrms	2500Vrms	2500Vrms
Specifications: Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Molding resin*4/Insulation sheet	Insulation sheet	Insulation sheet
Specifications: RoHS directive*6	Compliant	Compliant	Compliant	Compliant	Compliant*3	Compliant	Compliant
Specifications: Pin type*7	Control side of Zigzag (Normal, Short)	Long	Long	Short	Control side of Zigzag, Short	–	–

★: New Product

[Notes] ＊1 : PSSxxS9xE6 has OT function, PSSxxS9xF6 has V_{OT} function
＊2 : AC60Hz,1minute.Corresponds to isolation voltage 2500Vrms in the case the convex-shaped heat sink
＊3 : High melting point solder (Lead Over 85%) is used for chip soldering of PSSxxS51F6 only.
＊4 : Molding resin insulation for PSSxxS51F6/-C
＊5 : PSS50NC1F6 is not included brake.
＊6 : RoHS directive (2011/65/EU and (EU) 2015/863)
＊7 : Refer the datasheet of each product for more detail

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect
RC-IGBT: Reverse conducting IGBT
HVIC: High Voltage IC
UV: Power supply Under Voltage protection
OT: Over Temperature protection
SC: Short Circuit protection
V_{OT}: Analog Temperature Output
RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment
CIB: Converter Inverter Brake,
CI: Converter Inverter

Application circuit of super mini DIPIPM™



Lineup of DIPIPM™

Series Matrix of 1200V DIPIPM™

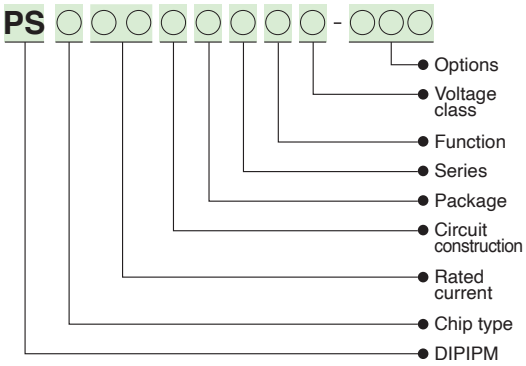
V_{CES}		1200V				
Series / I_C		Mini		Large	DIPIPM+	Large DIPIPM+
		Ver.7	—	Ver.6	CIB/CI	CI
5A			PSS05S72FT	PSS05SA2FT	PSS05MC1FT PSS05NC1FT*1	
10A			PSS10S72FT	PSS10SA2FT	PSS10MC1FT PSS10NC1FT*1	
15A		PSS15S73FT★		PSS15SA2FT	PSS15MC1FT PSS15NC1FT*1	
25A		PSS25S73FT★		PSS25SA2FT	PSS25MC1FT PSS25NC1FT*1	
35A				PSS35SA2FT	PSS35MC1FT PSS35NC1FT*1	
50A				PSS50SA2FT		PSS50NE1CT★
75A				PSS75SA2FT		PSS75NE1CT★
100A						PSS100NE1CT★
Chip		CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
Protective Function	UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side/Brake	P-side/N-side
	SC	N-side	N-side	N-side	N-side	N-side
	OT	—	—	—	—	—
	V_{OT}	N-side	N-side	N-side	N-side	N-side
Specifications	Active input	High(5V)	High(5V)	High(5V)	High(5V)	High(3/5V)
	Emitter pin of N-side	Open	Open	Open	Open	Open
	Fault output	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
	Insulation voltage	2500Vrms	2500Vrms	2500Vrms	2500Vrms	2500Vrms
	Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet
	RoHS directive*2	Compliant	Compliant	Compliant	Compliant	Compliant
	Pin type	—	—	—	—	—

★: New Product

[Notes] ＊1: PSS**NC1FT is not included brake
＊2: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect
UV: Supply Under Voltage protection
OT: Over Temperature protection
SC: Short Circuit protection
V_{OT}: Analog Temperature Output
RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment
CIB: Converter Inverter Brake
CI: Converter Inverter

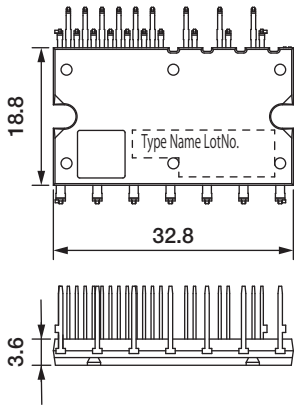
Type Name Definition of DIPIPM™



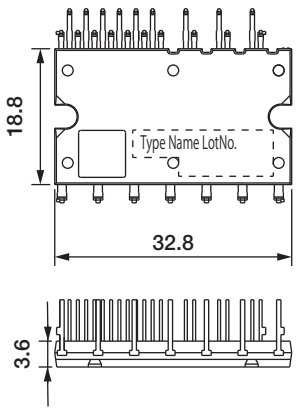
Outline Drawing of DIPIPM™

Unit:mm

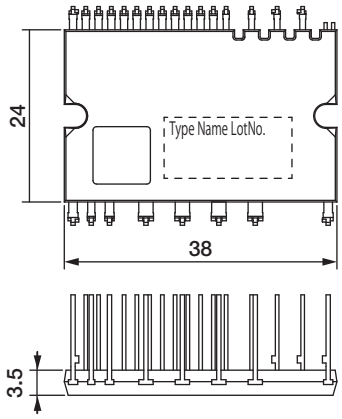
SLIMDIP
Normal



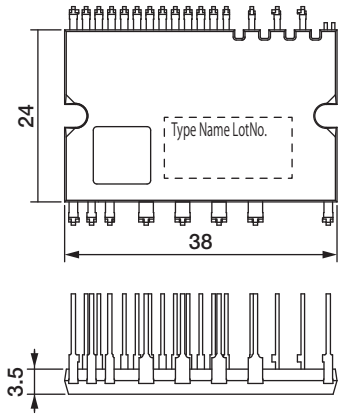
SLIMDIP
Short



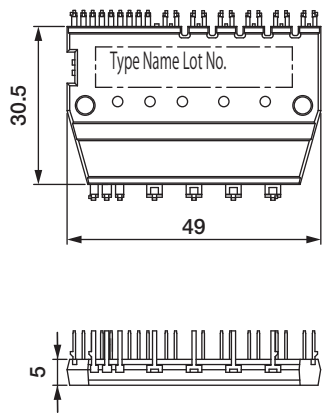
Super mini DIPIPM Ver.6
Long



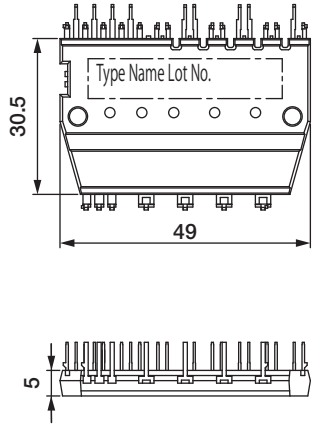
Super mini DIPIPM Ver.7
Long



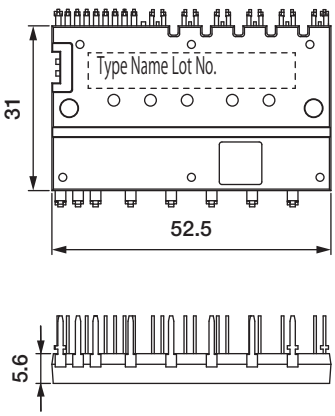
Mini DIPIPM (PSSxxS51F6)



Mini DIPIPM(PSSxxS51F6)
Control side of Zigzag



Mini DIPIPM (PSSxxS7xF6)
1200V Mini DIPIPM Ver.7
1200V Mini DIPIPM

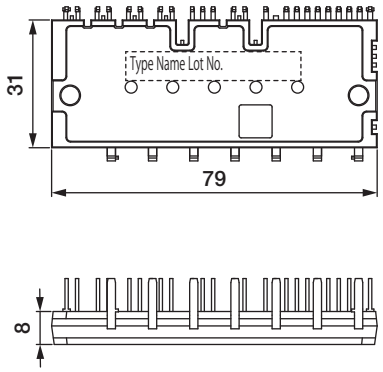


Lineup of DIPIPM™

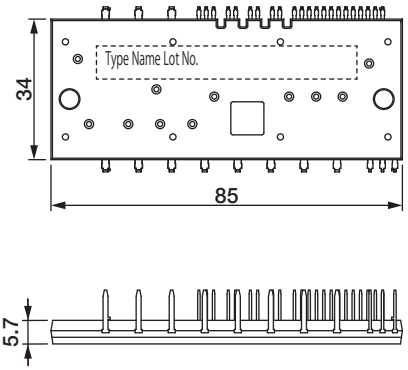
Outline Drawing of DIPIPM™

Unit:mm

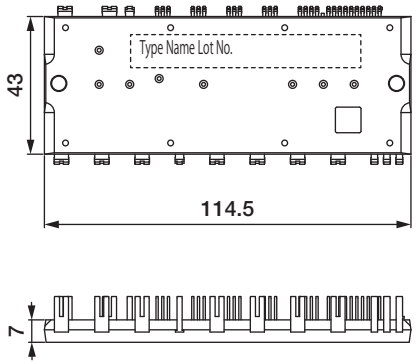
Large DIPIPM



DIPIPM+



Large DIPIPM+



Series , Main Application

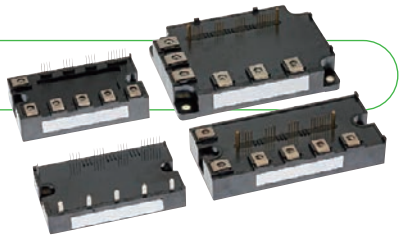
Series	Main Application
G1	Motion control/Renewable energy/Power supply
L1	
S1	
V1	
Photovoltaic	Photovoltaic
L	Motion control/Renewable energy/Power supply

Data sheet here

Rated Lineup

		Rated current											
		25A	35A	50A	75A	100A	150A	200A	300A	400A	450A	500A	600A	800A
Rated voltage	600V													
	650V													
	1200V													

Featured Products



Loaded with built-in functions, contributing to inverters with enhanced energy savings

G1 Series IPM with 7th-generation IGBT

<Main Features>
- Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT™*1 and a diode incorporating a RFC*2 structure that contributes to reducing the power consumed in inverters
- The new resin-insulated metal baseplate, originally introduced in 7th-generation IGBT modules, eliminates the solder-attached section, increasing the thermal cycle lifetime and improving inverter reliability
- In addition to the built-in functions of the previous product,*3 automatic switching speed control, and error detection function contribute to lowering inverter loss and shortening design time

*1 CSTBT™: Mitsubishi Electric's unique IGBT that utilizes the carrier cumulative effect
*2 RFC: Relaxed field cathode
*3 Conventional product: IPM L1-Series
Built-in functions: Supply Undervoltage lock protection (UV)、Short-circuit protection (SC), Over-temperature protection (OT)

■ "A" package main pin shape and layout

For the "A" package 6-in-1 (CG1A) main pin shape, select either solder pin or screw type
For the pin layout, select either straight or L-shaped

Main pin shape

Main pin: Solder pin

Main pin: Screw

Main pin layout

Straight

L-shaped

Lineup of IPM

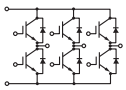
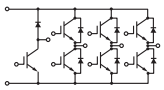
Matrix of IPM 650V/600V (No.: Number of outline drawing, see page 23 to 24)

V_{CES} / Series / I_C	650V			600V																	
	G1 Series	Connection	No.	L1 Series	Connection	No.	S1 Series	Connection	No.	V1 Series	Connection	No.	Photovoltaic	Connection	No.	L Series	Connection	No.
50A	PM50CG1A065	C	12	PM50CL1A060	C	01	PM50CS1D060	C	05				PM50B4LA060	B4	01			
	PM50RG1A065	R	12	PM50CL1B060	C	02							PM50B5LA060	B5	01			
	PM50CG1B065	C	10	PM50RL1A060	R	01							PM50B6LA060	B6	01			
	PM50RG1B065	R	10	PM50RL1B060	R	02							PM50B4LB060	B4	02			
	PM50CG1AL065	C	12	PM50RL1C060	R	03							PM50B5LB060	B5	02			
	PM50CG1AP065	C	09										PM50B6LB060	B6	02			
	PM50CG1APL065	C	09										PM50B4L1C060	B4	03			
	PM50RG1AP065	R	09										PM50B5L1C060	B5	03			
													PM50B6L1C060	B6	03			
75A	PM75CG1A065	C	12	PM75CL1A060	C	01	PM75CS1D060	C	05				PM75B4LA060	B4	01			
	PM75RG1A065	R	12	PM75CL1B060	C	02							PM75B5LA060	B5	01			
	PM75CG1B065	C	10	PM75RL1A060	R	01							PM75B6LA060	B6	01			
	PM75RG1B065	R	10	PM75RL1B060	R	02							PM75B4LB060	B4	02			
	PM75CG1AL065	C	12										PM75B5LB060	B5	02			
	PM75CG1AP065	C	09										PM75B6LB060	B6	02			
	PM75CG1APL065	C	09										PM75B4L1C060	B4	03			
	PM75RG1AP065	R	09										PM75B5L1C060	B5	03			
													PM75B6L1C060	B6	03			
100A	PM100CG1A065	C	12	PM100CL1A060	C	01	PM100CS1D060	C	05									
	PM100CG1B065	C	10	PM100CL1B060	C	02												
	PM100RG1B065	R	10	PM100RL1A060	R	01												
	PM100CG1AL065	C	12	PM100RL1B060	R	02												
	PM100CG1AP065	C	09															
	PM100CG1APL065	C	09															
150A	PM150CG1B065	C	10	PM150CL1A060	C	01	PM150CS1D060	C	05									
	PM150RG1B065	R	10	PM150CL1B060	C	02												
				PM150RL1A060	R	01												
				PM150RL1B060	R	02												
200A	PM200CG1B065	C	10	PM200CL1A060	C	04	PM200CS1D060	C	05									
	PM200RG1B065	R	10	PM200RL1A060	R	04												
	PM200CG1C065	C	11															
	PM200RG1C065	R	11															
300A	PM300CG1C065	C	11	PM300CL1A060	C	04												
	PM300RG1C065	R	11	PM300RL1A060	R	04												
400A										PM400DV1A060	D	06						
450A	PM450CG1C065	C	11													PM450CLA060	C	08
	PM450RG1C065	R	11															
600A										PM600DV1A060	D	06				PM600CLA060	C	08
800A										PM800DV1B060	D	07						
IGBT chip	CSTBT*1 Emitter sensor installed Temperature sensor installed			CSTBT*1 Built-in emitter sensor Built-in temperature sensor			CSTBT*1 Built-in emitter sensor Built-in temperature sensor			CSTBT*1 Built-in emitter sensor Built-in temperature sensor			CSTBT*1 Built-in emitter sensor Built-in temperature sensor			CSTBT*2 Built-in emitter sensor Built-in temperature sensor		
Fault output UV	P-side/N-side			P-side/N-side			N-side			P-side/N-side			P-side/N-side			P-side/N-side		
Fault output OT	P-side/N-side			P-side/N-side			N-side			P-side/N-side			P-side/N-side			P-side/N-side		
Fault output SC	P-side/N-side			P-side/N-side			N-side			P-side/N-side			P-side/N-side			P-side/N-side		
Identification	P-side/N-side			—			—			—			—			—		
RoHS directive*3	Compliant			Compliant			Compliant			Compliant			Compliant			Compliant		
Compatibility	—			L Series			S-DASH SERVO			V Series			—			—		
Connection	D	B4		B5			B6			C			R					

[Notes] *1: Full-gate CSTBT™ *2: PCM (Plugged Cell Merged) CSTBT™
*3: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] UV: Power supply Under Voltage protection
SC: Short Circuit protection
OT: Over Temperature protection
RoHS: Restriction of hazardous substances in electrical and electronic equipment

Matrix of IPM 1200V (No.: Number of outline drawing, see page 23 to 24)

V_{CES} / Series / I_C	1200V																	
	G1 Series	Connection	No.	L1 Series	Connection	No.				S1 Series	Connection	No.				V1 Series	Connection	No.	L Series	Connection	No.
25A	PM25CG1A120	C	12	PM25CL1A120	C	01				PM25CS1D120	C	05									
	PM25CG1B120	C	10	PM25CL1B120	C	02															
	PM25RG1A120	R	12	PM25RL1A120	R	01															
	PM25RG1B120	R	10	PM25RL1B120	R	02															
	PM25CG1AL120	C	12	PM25RL1C120	R	03															
	PM25CG1AP120	C	09																		
	PM25CG1APL120	C	09																		
	PM25RG1AP120	R	09																		
35A	PM35CG1A120	C	12																		
	PM35CG1B120	C	10																		
	PM35RG1A120	R	12																		
	PM35RG1B120	R	10																		
	PM35CG1AL120	C	12																		
	PM35CG1AP120	C	09																		
	PM35CG1APL120	C	09																		
	PM35RG1AP120	R	09																		
50A	PM50CG1A120	C	12																		
	PM50CG1B120	C	10	PM50CL1A120	C	01				PM50CS1D120	C	05									
	PM50RG1B120	R	10	PM50CL1B120	C	02															
	PM50CG1AL120	C	12	PM50RL1A120	R	01															
	PM50CG1AP120	C	09	PM50RL1B120	R	02															
	PM50CG1APL120	C	09																		
75A	PM75CG1B120	C	10	PM75CL1A120	C	01				PM75CS1D120	C	05									
	PM75RG1B120	R	10	PM75CL1B120	C	02															
				PM75RL1A120	R	01															
				PM75RL1B120	R	02															
100A	PM100CG1B120	C	10	PM100CL1A120	C	04				PM100CS1D120	C	05									
	PM100CG1C120	C	11	PM100RL1A120	R	04															
	PM100RG1B120	R	10																		
	PM100RG1C120	R	11																		
150A	PM150CG1C120	C	11	PM150CL1A120	C	04															
	PM150RG1C120	R	11	PM150RL1A120	R	04															
200A	PM200CG1C120	C	11													PM200DV1A120	D	06	PM200CLA120	C	08
	PM200RG1C120	R	11																		
300A																PM300DV1A120	D	06	PM300CLA120	C	08
450A																PM450DV1A120	D	06	PM450CLA120	C	08
IGBT chip	CSTBT*1 Emitter sensor installed Temperature sensor installed			CSTBT*1 Built-in current sensor Built-in temperature sensor						CSTBT*1 Built-in current sensor Built-in temperature sensor						CSTBT*1 Built-in current sensor Built-in temperature sensor			CSTBT*2 Built-in current sensor Built-in temperature sensor		
Fault output UV	P-side/N-side			P-side/N-side						N-side						P-side/N-side			P-side/N-side		
Fault output OT	P-side/N-side			P-side/N-side						N-side						P-side/N-side			P-side/N-side		
Fault output SC	P-side/N-side			P-side/N-side						N-side						P-side/N-side			P-side/N-side		
Identification	P-side/N-side			—						—						—			—		
RoHS directive*3	Compliant			Compliant						Compliant						Compliant			Compliant		
Compatibility	—			L Series						S-DASH SERVO						V Series			—		
Connection	D 			C 						R 											

[Notes] *1: Full-gate CSTBT™ *2: PCM (Plugged Cell Merged) CSTBT™
*3: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect
UV: Power supply Under Voltage protection
SC: Short Circuit protection
OT: Over Temperature protection
RoHS: the Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

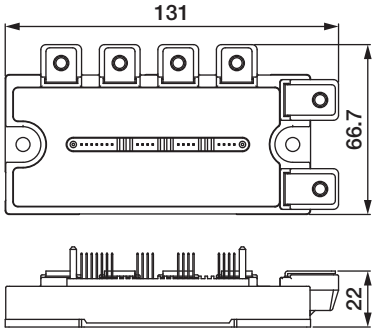
Lineup of IPM

Outline Drawing of IPM

Unit:mm

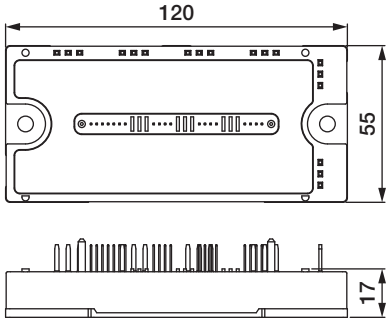
01

PM50,75,100,150CL1A/RL1A060
PM25,50,75CL1A/RL1A120
PM50,75B4/B5/B6LA060



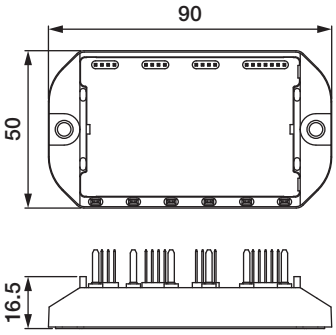
02

PM50,75,100,150CL1B/RL1B060
PM25,50,75CL1B/RL1B120
PM50,75B4/B5/B6LB060



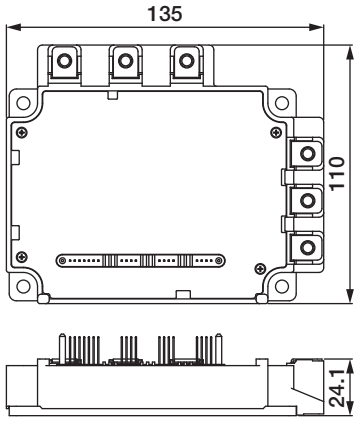
03

PM50RL1C060
PM25RL1C120
PM50,75,B4/B5/B6L1C060



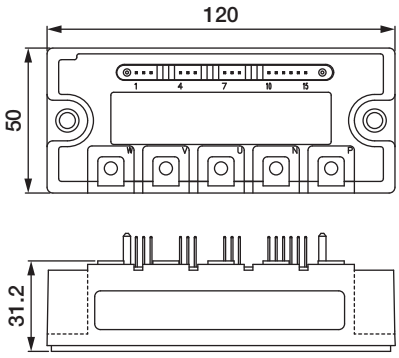
04

PM200,300CL1A/RL1A060
PM100,150CL1A/RL1A120



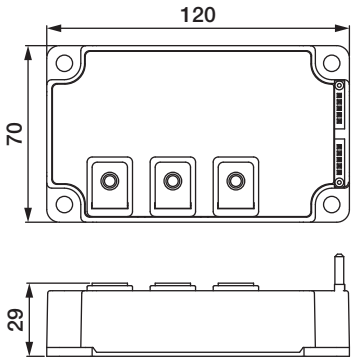
05

PM50,75,100,150,200CS1D060
PM25,50,75,100CS1D120



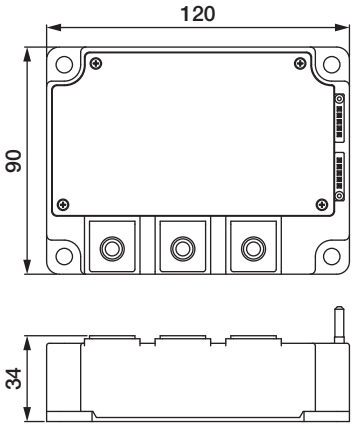
06

PM400,600DV1A060
PM200,300,450DV1A120



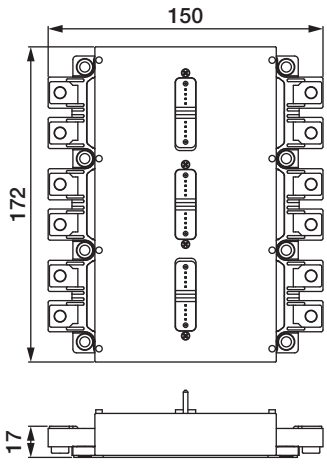
07

PM800DV1B060



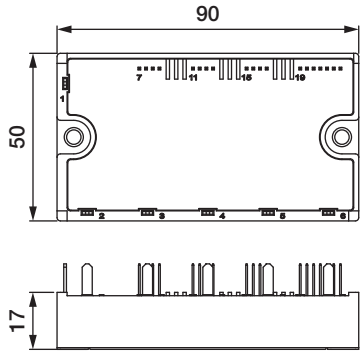
08

PM450,600CLA060
PM200,300,450CLA120



09

PM50,75,100CG1AP/CG1APL065
PM50,75RG1AP065
PM25,35,50CG1AP/CG1APL120
PM25,35RG1AP120

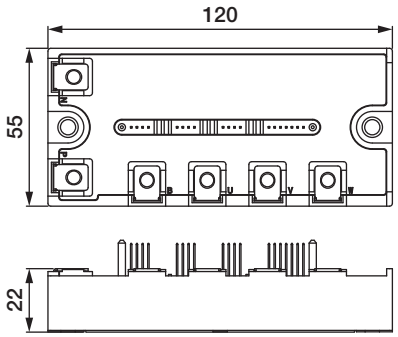


Outline Drawing of IPM

Unit:mm

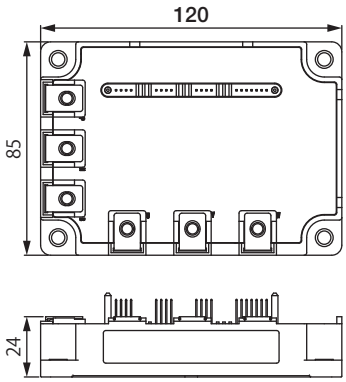
10

PM50,75,100,150,200CG1B/ RG1B065
PM25,35,50,75,100CG1B/ RG1B120



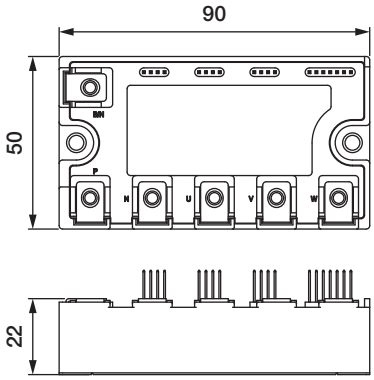
11

PM200,300,450CG1C/ RG1C065
PM100,150,200CG1C/ RG1C120



12

PM50,75,100CG1A/CG1AL065
PM50,75RG1AP065
PM25,35,50CG1A/CG1AL120
PM25,35RG1A120

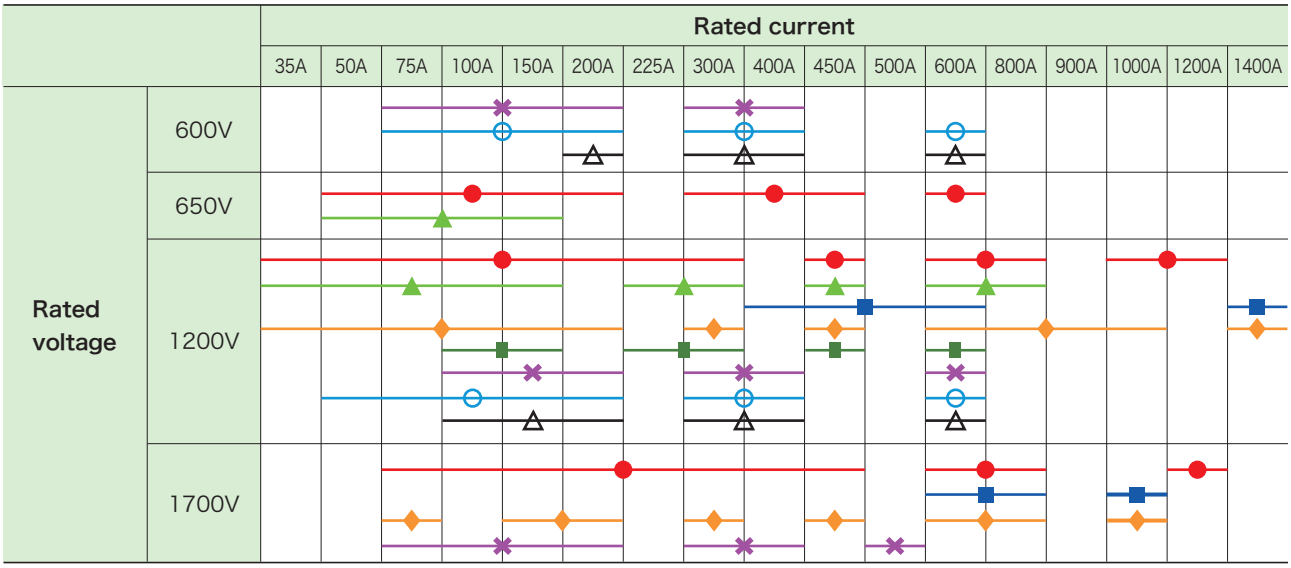


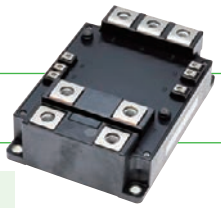
Series , Main Application

Series	Main Application
T	Motion control/Renewable energy /Power supply
T1	
For 3-level Inverters	
S	
S1	
A	
NF	
NF(NFH type)	

Data sheet here

Rated Lineup





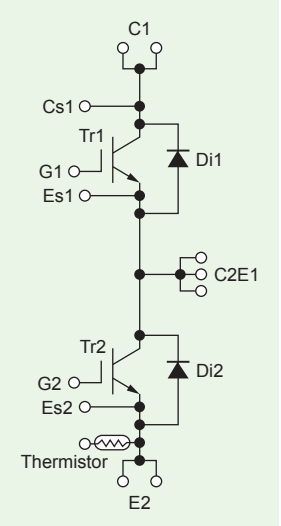
New Products

Industrial IGBT module with new standard package "LV100" for high power density inverter

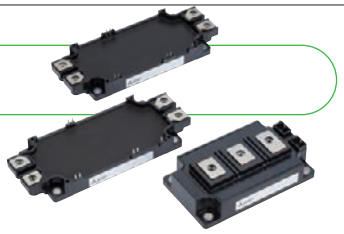
IGBT module T-series (LV100 for industrial)

IGBT module 2in1 type
■Lineup
800A/1700V, 800A/1700V(with enhanced FWD), 1200A/1700V
800A/1200V, 1200A/1200V 2in1 type

〈Main Features〉
・Next generation high capacity standard package for industrial use
・Improved ease of use by applying low impedance package
・Reducing the switching loss and optimal for the applications that are used in 1 to 5KHz
・Isolation voltage 4kV



Featured Products



New lineup contributes to simple design downsizing, energy-savings of industrial inverters.

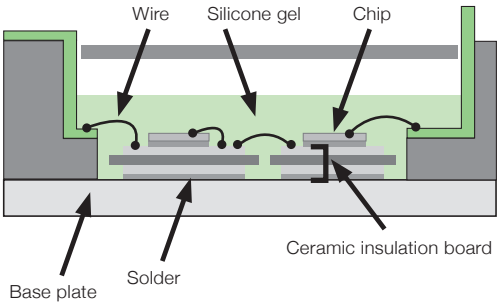
IGBT Module T/T1-Series

<Main Features>
- New modules equipped with three-phase converter, inverter, and brake circuit(CIB), contributes to simplifying design for inverter systems
- CIB modules contribute to compact inverter systems by reducing package size by 36% compared to the Mitsubishi Electric's existing module.(CIB)
- Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT™*2 and a diode incorporating a relaxed field of cathode (RFC) structure
- The new structure introduced eliminates the solder-attached section, increasing the thermal cycle lifetime, which contributes to improving the reliability of inverters
- The introduction of press-fit pins and PC-TIM*1 contribute to simplifying the assembly process for inverters

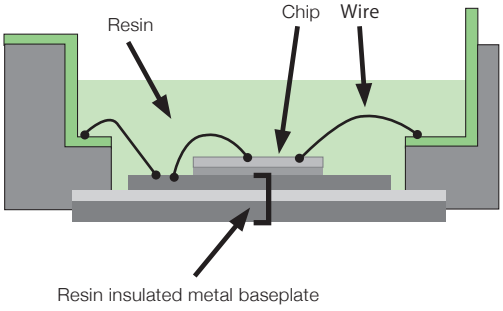
*1 PC-TIM: Phase change - thermal interface material
*2 CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

New structure realizes improved reliability (improved thermal cycle lifetime)

NX package structure comparison
6th-generation IGBT

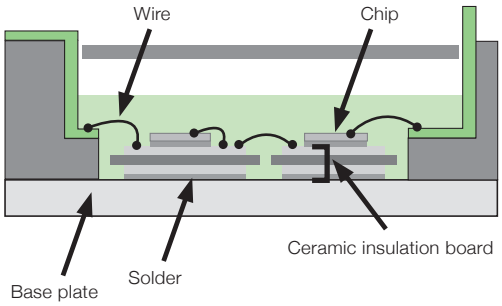


7th-generation IGBT

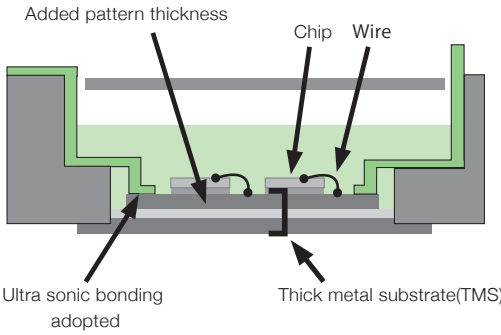


※Adopts SoLid Cover(SLC) Technology

Compared to standard (std) package structure
6th-generation IGBT



7th-generation IGBT

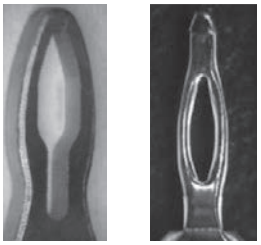


※Standard package is not available for CIB

◆ Press-fit terminal support (NX)

- Possible to select the control pin shape (soldered terminals/press-fit terminals)
- Solder attachment process eliminated

■Press-fit pin



①Main pin ②Signal pin

Lineup of IGBT Modules

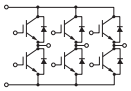
Matrix of IGBT Modules 650V/600V (No.: Number of outline drawing, see page 30 to 35)

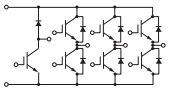
RoHS directive (2011/65/EU, (EU)2015/863) compliant

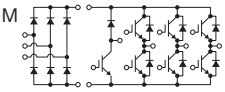
VCES	650V						600V											
Series / IC	T/T1-Series NX Type	Connection	No.	T-Series std Type	Connection	No.	A-Series NX Type	Connection	No.	NF-Series	Connection	No.	NF-Series NFH Type	Connection	No.
50A	CM50MXUB-13T CM50MXUB-13T1 CM50MXUBP-13T CM50MXUBP-13T1	M M M M	42 42 46 46												
75A	CM75MXUB-13T CM75MXUB-13T1 CM75MXUBP-13T CM75MXUBP-13T1	M M M M	42 42 46 46				CM75MX-12A	M	01	CM75TL-12NF CM75RL-12NF	T R	07 07			
100A	CM100TX-13T CM100TXP-13T CM100MXUB-13T CM100MXUB-13T1 CM100MXUBP-13T CM100MXUBP-13T1 CM100MXUD-13T CM100MXUD-13T1 CM100MXUDP-13T CM100MXUDP-13T1	T T M M M M M M M M	33 37 42 42 46 46 44 44 48 48	CM100DY-13T	D	30	CM100MX-12A CM100RX-12A	M R	01 02	CM100TL-12NF CM100RL-12NF	T R	07 07			
150A	CM150TX-13T CM150TXP-13T CM150RX-13T CM150RXP-13T CM150MXUD-13T CM150MXUD-13T1 CM150MXUDP-13T CM150MXUDP-13T1	T T R R M M M M	33 37 34 38 44 44 48 48	CM150DY-13T	D	30	CM150RX-12A	R	02	CM150DY-12NF CM150TL-12NF CM150RL-12NF	D T R	08 07 07			
200A	CM200TX-13T CM200TXP-13T CM200RX-13T CM200RXP-13T	T T R R	33 37 34 38	CM200DY-13T	D	30	CM200RX-12A	R	02	CM200DY-12NF CM200TL-12NF CM200RL-12NF	D T R	08 09 09	CM200DU-12NFH	D	13
225A															
300A	CM300DX-13T CM300DXP-13T	D D	28 39	CM300DY-13T	D	31	CM300DX-12A	D	03	CM300DY-12NF	D	08	CM300DU-12NFH	D	14
400A				CM400DY-13T	D	31	CM400DX-12A	D	03	CM400DY-12NF	D	10	CM400DU-12NFH	D	14
450A	CM450DX-13T CM450DXP-13T	D D	28 39												
600A	CM600DX-13T CM600DXP-13T	D D	28 39	CM600DY-13T	D	32				CM600DY-12NF	D	11	CM600DU-12NFH	D	15
1000A															

Connection

D 

T 

R 

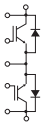
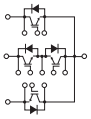
M 

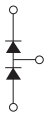
Matrix of Power Modules for 3-level Inverter (No.: Number of outline drawing, see page 31 to 33)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

VCES/VRRM	1200 V IGBT Module			1700 V IGBT Module			1200 V Diode Module			1700 V Diode Module		
IC/IF	T/S/S1-Series std Type	Connection	No.	S/S1-Series std Type	Connection	No.	S/S1-Series std Type	Connection	No.	S/S1-Series std Type	Connection	No.
400A	CM400ST-24S1 CM400C1Y-24S	S C1	35 11									
450A	CM450C1Y-24T	C1	32									
500A	CM500C2Y-24S	C2	36									
600A	CM600C1Y-24T	C1	32	CM600HA-34S	H	36				RM600DY-34S	D	32
800A				CM800HA-34S	H	36				RM800DY-34S	D	32
1000A				CM1000HA-34S	H	36						
1400A	CM1400HA-24S	H	36				RM1400HA-24S★	H	36			

Connection

IGBT module C1  C2  H  S 

Diode module H  D 

∗Connection of diode module and IGBT module are different.

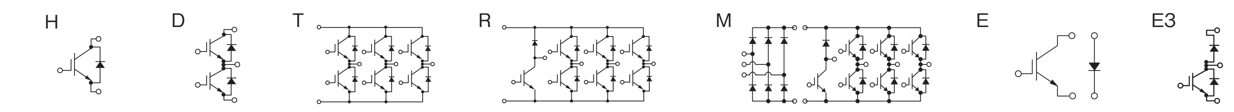
★: New Product

Matrix of IGBT Modules 1200V (No.: Number of Outline Drawing, see page 30 to 35)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

VCES	1200V																				
Series / Ic	T-Series LV100 Type	Connection	No.	T/T1-Series NX Type	Connection	No.	T-Series std Type	Connection	No.	S/S1-Series NX Type	Connection	No.	S/S1-Series std Type	Connection	No.	S/S1-Series MPD Type	Connection	No.	A-Series*1 NF-Series*1	Connection	No.
35A				CM35MXUA-24T CM35MXUA-24T1 CM35MXUAP-24T CM35MXUAP-24T1	M M M M	41 41 45 45				CM35MXA-24S	M	04									
50A				CM50MXUA-24T CM50MXUA-24T1 CM50MXUAP-24T CM50MXUAP-24T1	M M M M	41 41 45 45				CM50MXA-24S	M	04							CM50RL-24NF CM50TL-24NF	R T	07 07
75A				CM75MXUB-24T CM75MXUB-24T1 CM75MXUBP-24T CM75MXUBP-24T1 CM75MXUC-24T CM75MXUC-24T1 CM75MXUCP-24T CM75MXUCP-24T1	M M M M M M M M	42 42 46 46 43 43 47 47				CM75MXA-24S CM75TX-24S CM75RX-24S	M T R	04 05 02							CM75RL-24NF CM75TL24NF	R T	07 07
100A				CM100TX-24T CM100TXP-24T CM100RX-24T CM100RXP-24T CM100MXUC-24T CM100MXUC-24T1 CM100MXUCP-24T CM100MXUCP-24T1	T T R R M M M M	33 37 34 38 43 43 47 47	CM100DY-24T	D	30	CM100MXA-24S CM100TX-24S1 CM100RX-24S1	M T R	04 25 26							CM100DY-24A CM100DY-24NF CM100E3Y-24NF CM100RL-24NF CM100TL-24NF CM100DU-24NFH	D D E3 R T D	08 08 08 07 07 13
150A				CM150TX-24T CM150TXP-24T CM150RX-24T CM150RXP-24T CM150MXUD-24T CM150MXUD-24T1 CM150MXUDP-24T CM150MXUDP-24T1	T T R R M M M M	33 37 34 38 44 44 48 48	CM150DY-24T	D	30	CM150DX-24S CM150EXS-24S CM150TX-24S1 CM150RX-24S1	D E T R	03 24 25 26							CM150DY-24A CM150DY-24NF CM150E3Y-24NF CM150RL-24NF CM150TL-24NF CM150DU-24NFH	D D E3 R T D	08 08 08 09 09 13
200A				CM200TX-24T CM200TXP-24T	T T	33 37	CM200DY-24T	D	31	CM200EXS-24S CM200RXL-24S	E R	24 21							CM200DY-24A CM200DY-24NF CM200RL-24NF CM200TL-24NF CM200DU-24NFH	D D R T D	08 10 09 09 14
225A				CM225DX-24T CM225DXP-24T CM225DX-24T1 CM225DXP-24T1	D D D D	28 39 28 39				CM225DX-24S1	D	27									
300A				CM300DX-24T CM300DXP-24T CM300DX-24T1 CM300DXP-24T1	D D D D	28 39 28 39	CM300DY-24T	D	31	CM300DX-24S1 CM300EXS-24S CM300RXL-24S1	D E R	27 24 21	CM300DY-24S	D	10				CM300DY-24A CM300DY-24NF CM300DU-24NFH	D D D	10 11 14
400A																			CM400DY-24A CM400HA-24A CM400DY-24NF CM400DU-24NFH	D H D D	11 16 11 15
450A				CM450DX-24T CM450DXP-24T CM450DX-24T1 CM450DXP-24T1	D D D D	28 39 28 39	CM450DY-24T	D	32	CM450DX-24S1	D	27	CM450DY-24S	D	11						
600A				CM600DX-24T CM600DXP-24T CM600DX-24T1 CM600DXP-24T1	D D D D	28 39 28 39	CM600DY-24T	D	32	CM600DX-24S1 CM600DXL-24S	D D	27 06	CM600DY-24S	D	11				CM600DY-24A CM600HA-24A CM600DU-24NF CM600DU-24NFH	D H D D	11 16 12 15
800A	CM800DW-24T	D	49	CM800DX-24T1 CM800DXP-24T1	D D	28 39							CM800DY-24S	D	12						
900A																CM900DUC-24S	D	17			
1000A				CM1000DX-24T CM1000DXP-24T	D D	29 40				CM1000DXL-24S	D	06									
1200A	CM1200DW-24T	D	49																		
1400A													CM1400HA-24S	H	36	CM1400DUC-24S	D	17			

Connection



*1: A-Series have model namse ending with A, NF-Series have model name ending with NF/NFH

Lineup of IGBT Modules

Matrix of IGBT Modules 1700V (No.: Number of Outline Drawing, see page 30 to 35)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

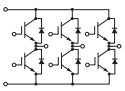
V_{CES}	1700V																							
Series / I_C	T-Series LV100 Type			T-Series NX Type			T-Series std Type			S/S1-Series NX Type			S/S1-Series std Type			S/S1-Series MPD Type			A-Series std Type		
		Connection	No.		Connection	No.		Connection	No.		Connection	No.		Connection	No.		Connection	No.		Connection	No.
75A							CM75DY-34T	D	30	CM75MXA-34SA CM75RX-34SA	M R	23 19							CM75DY-34A	D	08
100A				CM100TX-34T CM100TXP-34T	T T	33 37	CM100DY-34T	D	30										CM100DY-34A	D	08
150A				CM150TX-34T CM150TXP-34T	T T	33 37	CM150DY-34T	D	31	CM150DX-34SA CM150RXL-34SA	D R	20 21							CM150DY-34A	D	10
200A							CM200DY-34T	D	31	CM200DX-34SA CM200EXS-34SA	D E	20 24							CM200DY-34A	D	10
225A				CM225DX-34T CM225DXP-34T	D D	28 39															
300A				CM300DX-34T CM300DXP-34T	D D	28 39	CM300DY-34T	D	32	CM300DX-34SA	D	20							CM300DY-34A	D	11
400A							CM400DY-34T	D	32										CM400DY-34A	D	18
450A				CM450DX-34T CM450DXP-34T	D D	28 39				CM450DXL-34SA	D	22									
500A																			CM500HA-34A	H	16
600A				CM600DX-34T CM600DXP-34T	D D	28 39				CM600DXL-34SA	D	22	CM600HA-34S	H	36						
800A	CM800DW-34T CM800DW-34TA	D D	49 49										CM800HA-34S	H	36						
1000A													CM1000HA-34S	H	36	CM1000DUC-34SA	D	17			
1200A	CM1200DW-34T	D	49																		

Connection

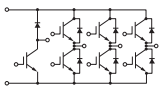
H

D

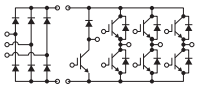
T



R



M

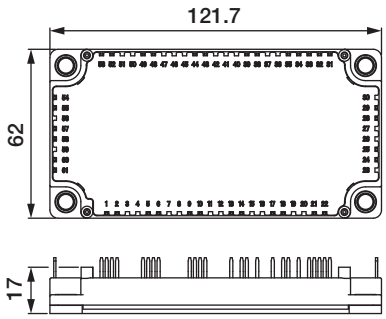


E

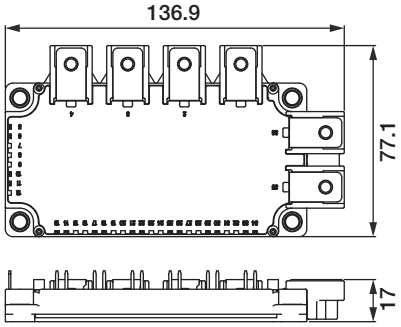
Outline Drawing of IGBT Modules

Unit:mm

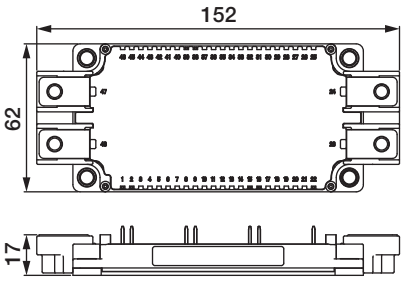
01 CM75,100MX-12A



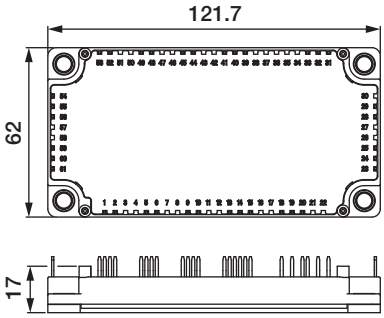
02 CM100,150,200RX-12A CM75RX-24S



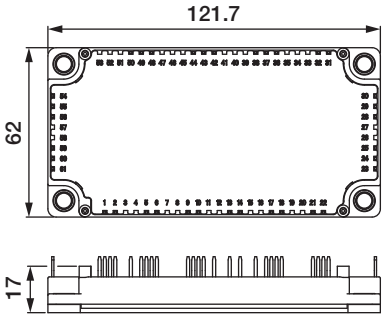
03 CM300,400DX-12A CM150,200DX-24S



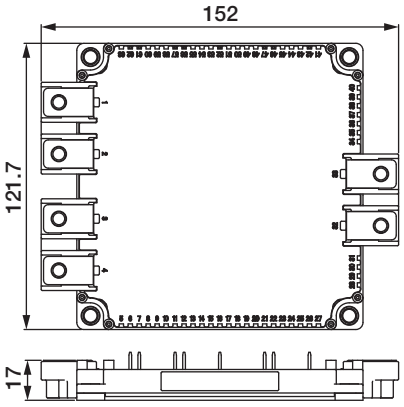
04 CM35,50,75,100MXA-24S



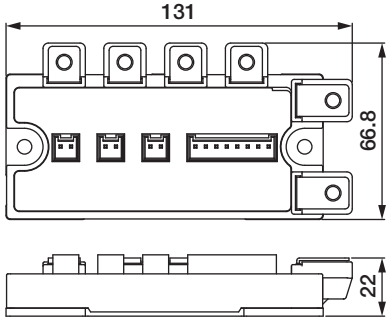
05 CM75TX-24S



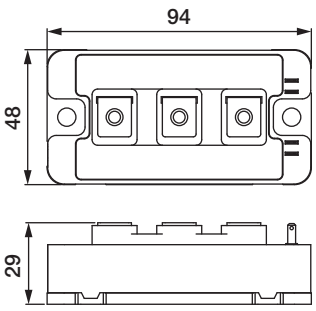
06 CM600,1000DXL-24S



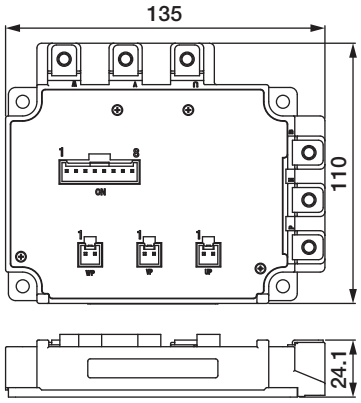
07 CM75,100,150TL/RL-12NF CM50,75,100TL/RL-24NF



08 CM150,200,300DY-12NF CM100,150DY-24NF CM100,150,200DY-24A CM75,100DY-34A CM100,150E3Y-24NF



09 CM200TL/RL-12NF CM150,200TL/RL-24NF



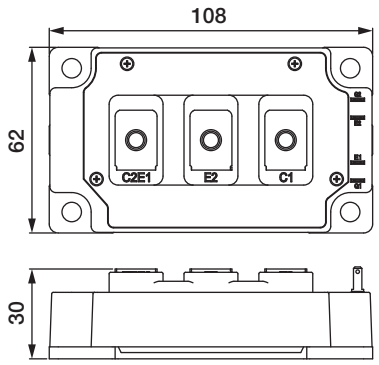
Lineup of IGBT Modules

Outline Drawing of IGBT Modules

Unit:mm

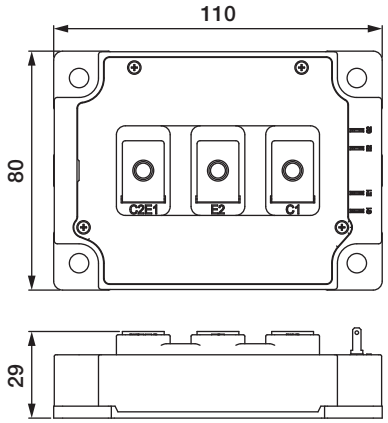
10

CM400DY-12NF
CM200DY-24NF
CM300DY-24A
CM300DY-24S
CM150,200DY-34A



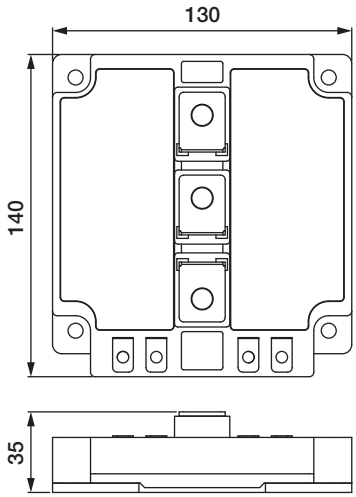
11

CM600DY-12NF
CM400DY-24NF
CM400,600DY-24A
CM300DY-34A
CM400C1Y-24S
CM450DY-24S
CM600DY-24S
CM300DY-24NF



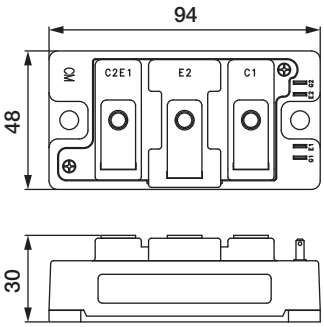
12

CM600DU-24NF
CM800DY-24S



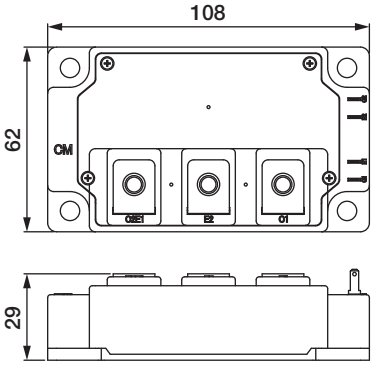
13

CM200DU-12NFH
CM100,150DU-24NFH



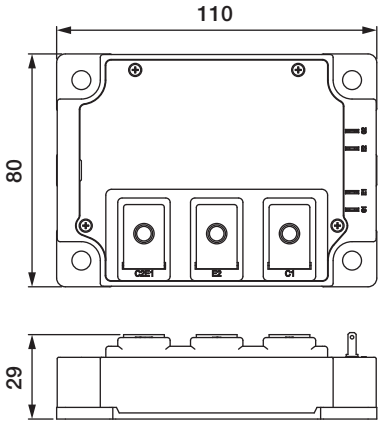
14

CM300,400DU-12NFH
CM200,300DU-24NFH



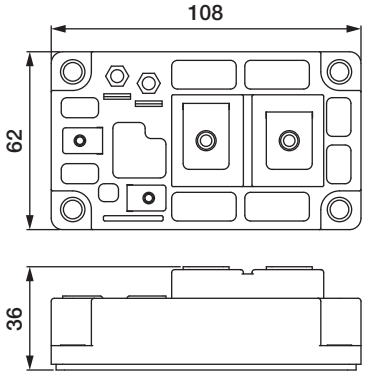
15

CM600DU-12NFH
CM400,600DU-24NFH



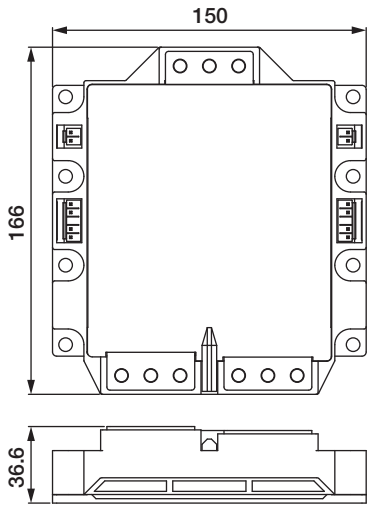
16

CM400,600HA-24A
CM500HA-34A



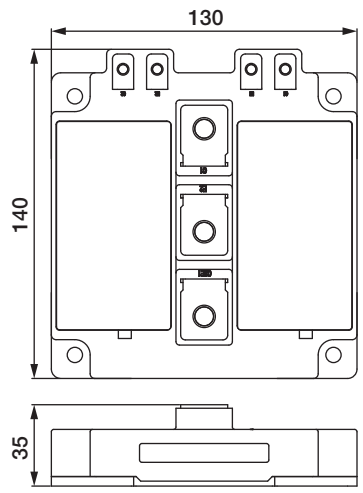
17

CM900,1400DUC-24S
CM1000DUC-34SA



18

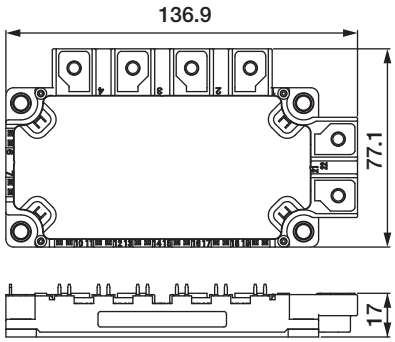
CM400DY-34A



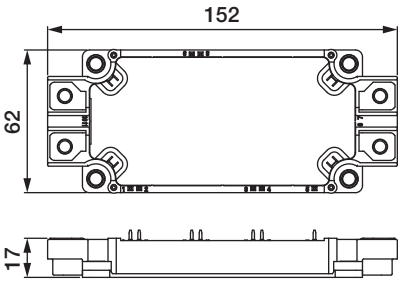
Outline Drawing of IGBT Modules

Unit:mm

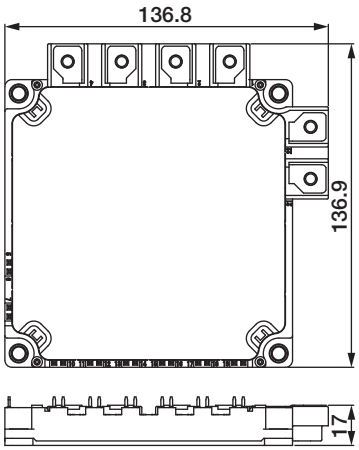
19 CM75RX-34SA



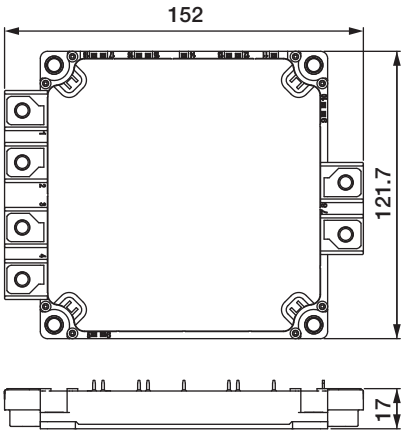
20 CM150DX-34SA CM200DX-34SA CM300DX-34SA



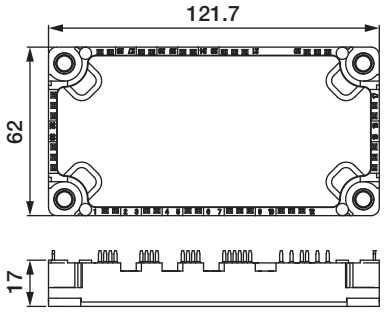
21 CM200RXL-24S CM300RXL-24S1 CM150RXL-34SA



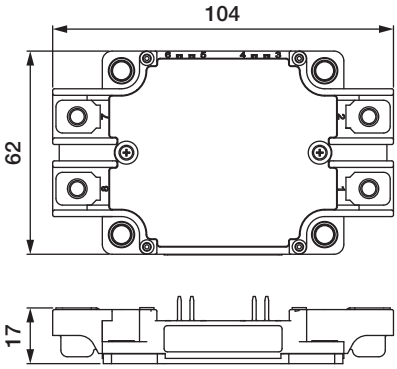
22 CM450DXL-34SA CM600DXL-34SA



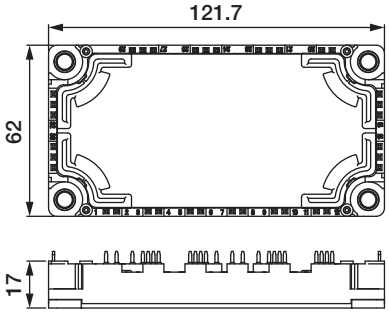
23 CM75MXA-34SA



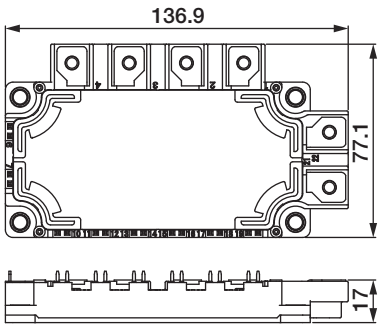
24 CM150EXS-24S CM200EXS-24S CM300EXS-24S CM200EXS-34SA



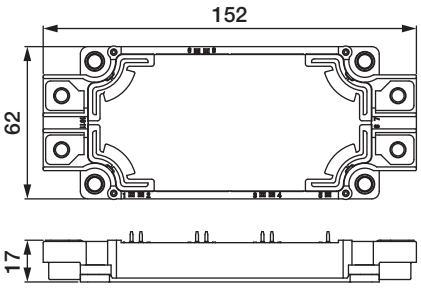
25 CM100TX-24S1 CM150TX-24S1



26 CM100RX-24S1 CM150RX-24S1



27 CM225DX-24S1 CM300DX-24S1 CM450DX-24S1 CM600DX-24S1

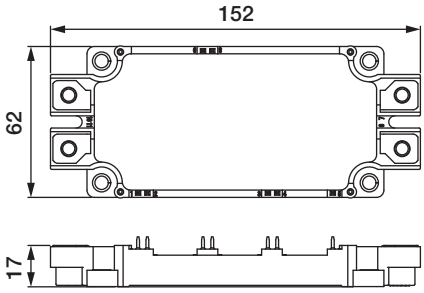


Lineup of IGBT Modules

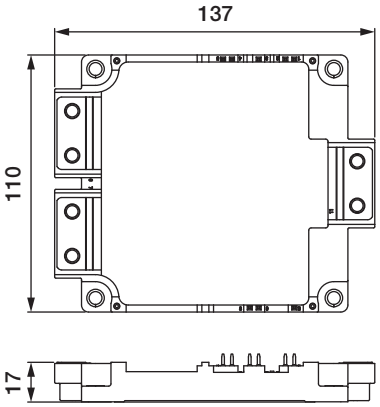
Outline Drawing of IGBT Modules

Unit:mm

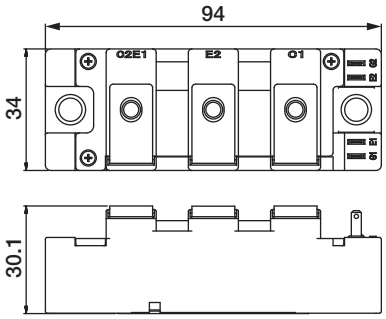
28
CM300,450,600DX-13T
CM225,300,450,600DX-24T
CM225,300,450,600,800DX-24T1
CM225,300,450DX,600DX-34T



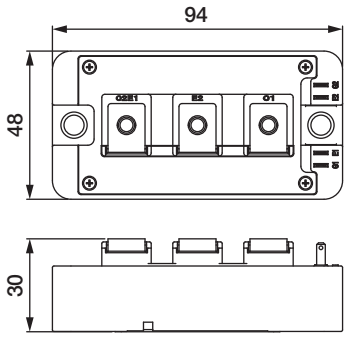
29
CM1000DX-24T



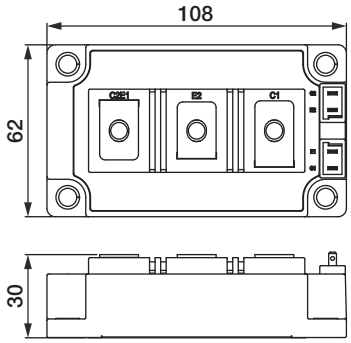
30
CM100,150,200DY-13T
CM100,150DY-24T
CM75,100DY-34T



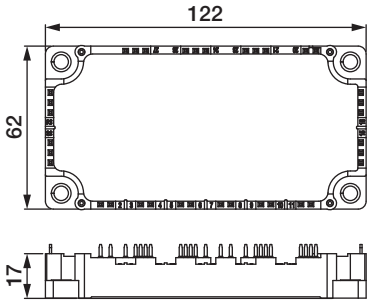
31
CM300,400DY-13T
CM200,300DY-24T
CM150,200DY-34T



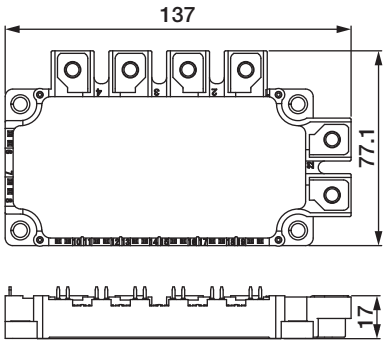
32
CM600DY-13T
CM450,600DY-24T
CM450,600C1Y-24T
CM300,400DY-34T
RM600,800DY-34S



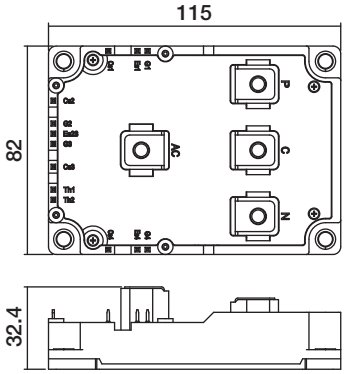
33
CM100,150,200TX-13T
CM100,150,200TX-24T
CM100,150TX-34T



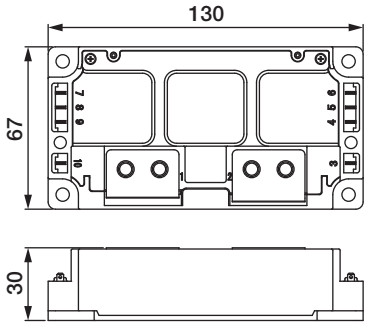
34
CM150,200RX-13T
CM100,150RX-24T



35
CM400ST-24S1



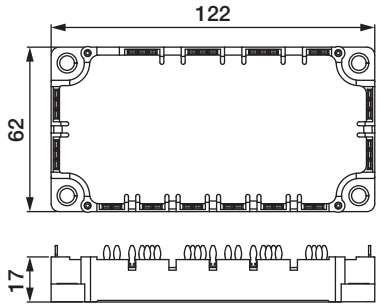
36
CM500C2Y-24S
CM1400HA-24S
CM600,800,1000HA-34S
RM1400HA-24S



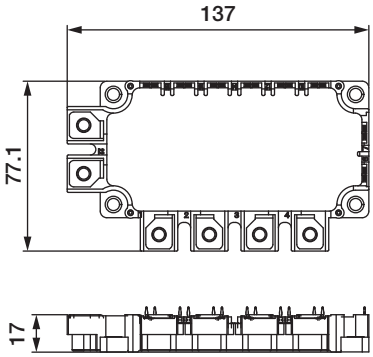
Outline Drawing of IGBT Modules

Unit:mm

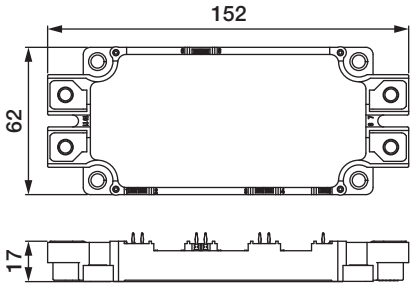
37
CM100,150,200TXP-13T
CM100,150,200TXP-24T
CM100,150TXP-34T



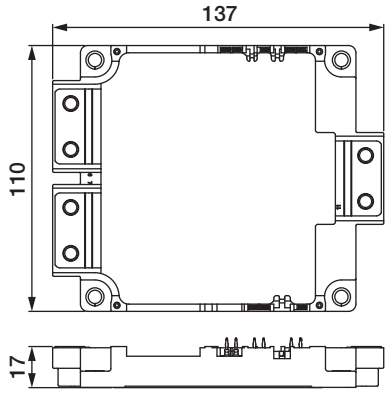
38
CM150,200RXP-13T
CM100,150RXP-24T



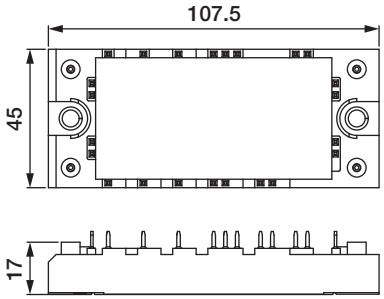
39
CM300,450,600DXP-13T
CM225,300,450,600DXP-24T
CM225,300,450,600,800DXP-24T1
CM225,300,450,600DXP-34T



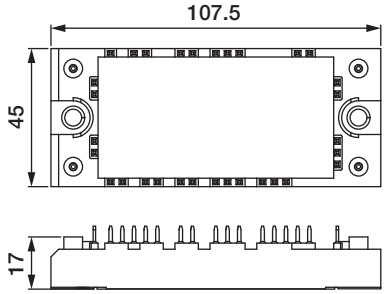
40
CM1000DXP-24T



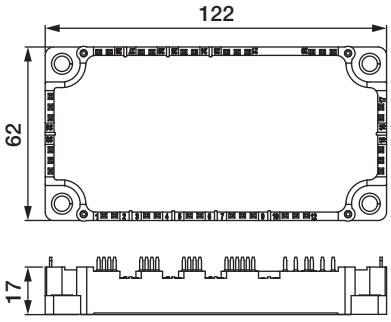
41
CM35,50MXUA-24T/24T1



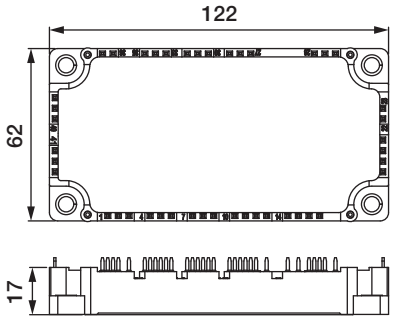
42
CM50,75,100MXUB-13T/13T1
CM75MXUB-24T/24T1



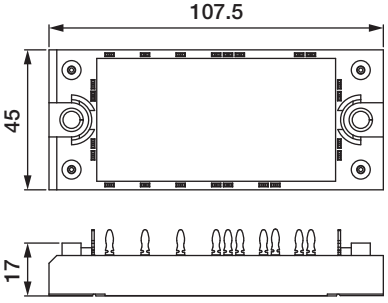
43
CM75,100MXUC-24T/24T1



44
CM100/150MXUD-13T/T1
CM150MXUD-24T/T1



45
CM35/50MXUAP-24T/T1

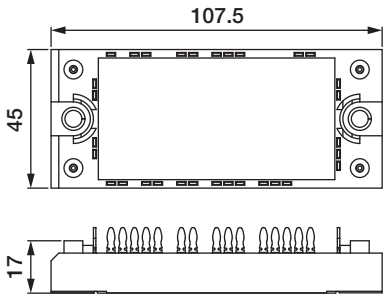


Lineup of IGBT Modules

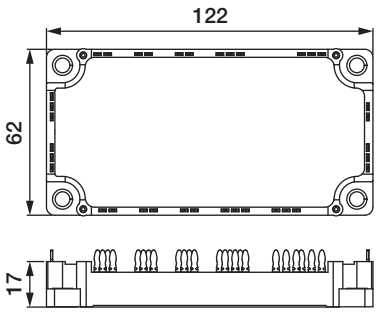
Outline Drawing of IGBT Modules

Unit:mm

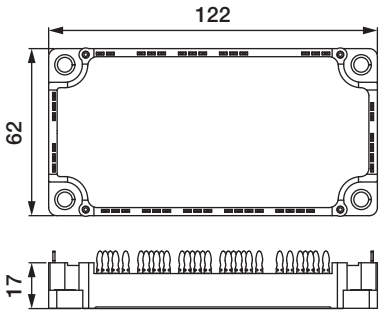
46 CM50/75/100MXUBP-13T/T1
CM75MXUBP-24T/T1



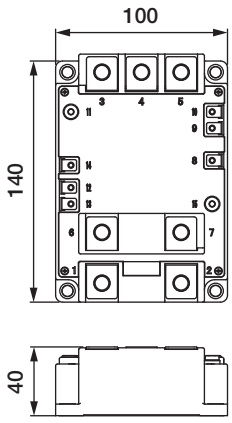
47 CM75/100MXUCP-24T/T1



48 CM100/150MXUDP-13T/T1
CM150MXUDP-24T/T1



49 CM800,1200DW-24T
CM800,1200DW-34T/TA



Series , Main Application

Series	Main Application
X	Traction/Power transmission/Motion control
R	
S	
N	
H	

Data sheet here

Rated Lineup

Rated voltage	Rated current: 200A	300A	400A	450A	600A	750A	800A	900A	1000A	1200A	1350A	1500A	1600A	1800A	2400A
1700V					●		◆ ■			● ■ ◆			●	◆	●
2500V			■				■			■					
3300V			■	●			■		▲	● ■		▲		●	
4500V				●	■		▲	●		▲	●				
6500V	■	●	■		● ■	▲		●	●						

New Products

X Series HVIGBT Modules std type

Existing compatible package: standard type contributes to smaller, higher-capacity inverter systems by expanding lineup

<Main Features>
- Power loss reduced by incorporating 7th-generation IGBT and RFC*1 diode
- Compared to the existing CM900HC-90H and CM1350HC-90X, the new models' rated output currents are 50% greater but external dimensions are the same.
- Compared to existing CM900HC-90H, new CM900HC-90X, etc. are 33% smaller but achieve the same voltage and current ratings.
- Optimal package internal structure realizes improved heat dissipation, humidity resistance and flame retardance, increasing product life

*1 RFC : Relaxed field of cathode

Product lineup

std type	1.7kV	3.3kV	4.5kV	6.5kV
	1600A 2400A	1200A	900A 1000A	600A
	2400A	1200A 1800A	900A 1350A 1500A	600A 900A 1000A

X Series HVIGBT Modules dual type

New common frame package: dual type class-leading current density contributes to increased power output in inverter systems

<Main Features>
- Power loss reduced by incorporating 7th-generation IGBT and RFC *1 diode
- Industry's highest 3.3kV/600A Si module power density of 8.57A/cm² *2 contributes to increased power output and efficiency
- Terminal layout optimized for easy paralleling and flexible inverter configurations and capacities
- New package structure offers extra reliability

*2 As of Dec. 17, 2020 based on Mitsubishi Electric research

Product lineup

LV100	1.7kV	3.3kV
	1200A	450A 600A

HV100	3.3kV	4.5kV	6.5kV
	450A 600A	450A	300A

Lineup of HVIGBT Modules

Series Matrix of HVIGBT (No.: Number of Outline Drawing, see page 39 to 40)

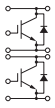
V_{CES} / I_C	1700V												2500V				3300V											
	X-Series				S-Series N-Series				H-Series				H-Series				X-Series				R-Series				H-Series			
	Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.	
400A													CM400DY-50H	D1	B	08									CM400HG-66H CM400DY-66H	H D1	G B	05 08
450A																	CM450DA-66X CM450DE-66X★	D2 D2	A E	09 10								
600A									CM600DY-34H CM600E2Y-34H	D1 E2	B B	01 01					CM600DA-66X CM600DE-66X★	D2 D2	A E	09 10								
800A					CM800DZB-34N	D1	C	01	CM800DZ-34H	D1	C	01	CM800HB-50H	H	B	03									CM800HC-66H CM800E4C-66H CM800E6C-66H	H E4 E2	C C C	03 04 04
1000A																					CM1000HC-66R CM1000E4C-66R	H E4	C C	03 04				
1200A	CM1200DA-34X★ CM1200E4C-34X※	D2 E4	A C	09 03	CM1200HCB-34N CM1200DC-34N CM1200E4C-34N CM1200DC-34S	H D1 E4 D1	C C C C	03 01 03 01	CM1200HC-34H	H	C	02	CM1200HC-50H	H	C	04	CM1200HC-66X CM1200HCB-66X CM1200E4C-66X※	H H E4	C C C	03 04 04					CM1200HG-66H CM1200HC-66H	H H	C C	06 04
1500A																					CM1500HC-66R CM1500HG-66R	H H	C G	04 06				
1600A	CM1600HC-34X※	H	C	03					CM1600HC-34H	H	C	02																
1800A					CM1800HC-34N CM1800HCB-34N	H H	C C	03 04	CM1800HC-34H	H	C	04					CM1800HC-66X CM1800HG-66X	H H	C G	04 06								
2400A	CM2400HC-34X CM2400HCB-34X★★	H H	C C	03 04	CM2400HC-34N CM2400HCB-34N	H H	C C	03 04	CM2400HC-34H	H	C	04																

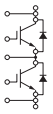
Connection

H 

E2/E6 

E4 

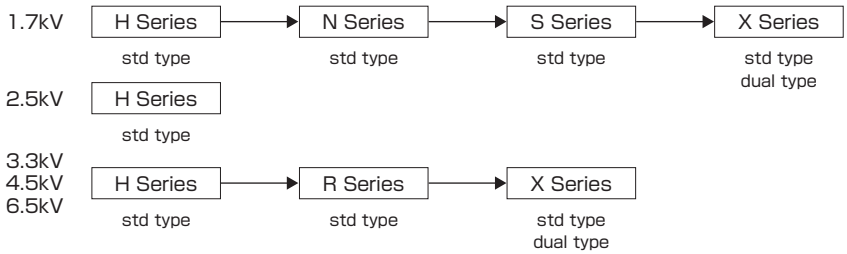
D1 

D2 

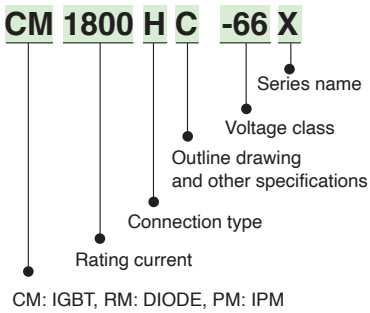
[Type]
A : Al base plate 6kV Isolation
B : Cu base plate 6kV Isolation
C : AlSiC base plate 6kV Isolation
G : AlSiC base plate 10kV Isolation
E : Al base plate 10kV Isolation

★★: Under Development ★: New Product
(※) Under consideration for development
The outline drawing is written the figure of principal part numbers that have a common dimension.

Evolution of HVIGBT Module Series



Type Name Definition of IGBT Modules



Series Matrix of HVIGBT (No.: Number of Outline Drawing, see page 39 to 40)

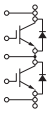
VCES / IC	4500V												6500V											
	X-Series				R-Series				H-Series				X-Series				R-Series				H-Series			
	Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.		Connection	Type	No.	
200A																					CM200HG-130H	H	G	05
300A													CM300DE-130X※	D2	E	10								
400A																					CM400HG-130H CM400E2G-130H CM400E4G-130H	H E2 E4	G G G	07 06 06
450A	CM450DE-90X※	D2	E	10																				
600A									CM600HG-90H	H	G	07	CM600HG-130X★ CM600HGB-130X※ CM600E4G-130X※	H H E4	G G G	07 06 06					CM600HG-130H	H	G	06
750A																	CM750HG-130R	H	G	06				
800A					CM800HC-90R CM800HG-90R	H H	C G	03 07																
900A	CM900HC-90X★★ CM900HG-90X CM900HGB-90X※	H H H	C G G	03 07 06					CM900HC-90H CM900HG-90H	H H	C G	04 06	CM900HG-130X	H	G	06								
1000A	CM1000HG-90X	H	G	07									CM1000HG-130XA	H	G	06								
1200A					CM1200HC-90R CM1200HC-90RA CM1200HG-90R	H H H	C C G	04 04 06																
1350A	CM1350HC-90X CM1350HG-90X	H H	C G	04 06																				
1500A	CM1500HC-90XA CM1500HG-90X	H H	C G	04 06																				

Connection

H 

E2/E6 

E4 

D2 

[Type]
A : Al base plate 6kV Isolation
B : Cu base plate 6kV Isolation
C : AlSiC base plate 6kV Isolation
G : AlSiC base plate 10kV Isolation
E : Al base plate 10kV Isolation

★★: Under Development ★: New Product
(※) Under consideration for development
The outline drawing is written the figure of principal part numbers that have a common dimension.

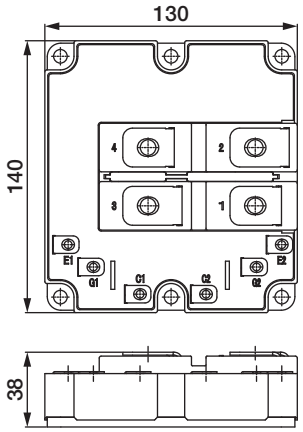
Lineup of HVIGBT Modules

Outline Drawing of HVIGBT Modules

Unit:mm

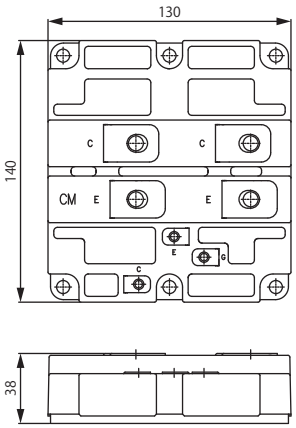
01

CM1200DC-34N/S
CM800DZB-34N
CM600DY/E2Y-34H
CM800DZ-34H



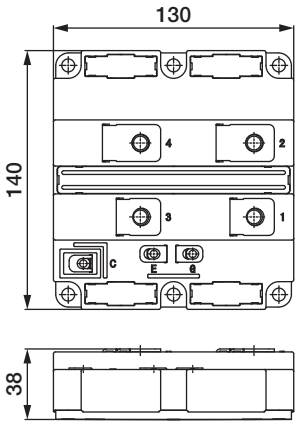
02

CM1200,1600HC-34H



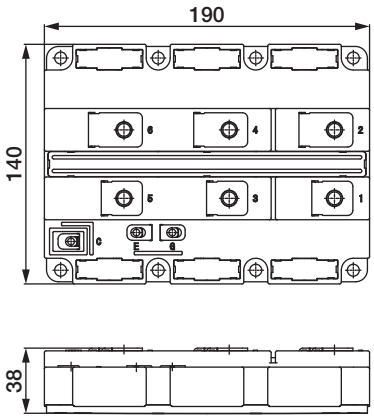
03

CM1200E4C-34X
CM1600, 2400HC-34X
CM1200HC-66X
CM900HC-90X
etc.



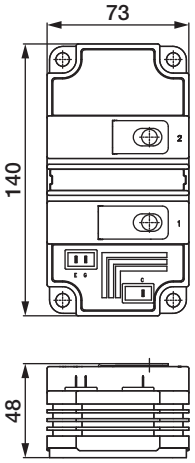
04

CM2400HCB-34X, CM1200E4C-66X
CM1200HCB-66X, CM1800HC-66X
CM1350HC-90X, CM1500HC-90XA
etc.



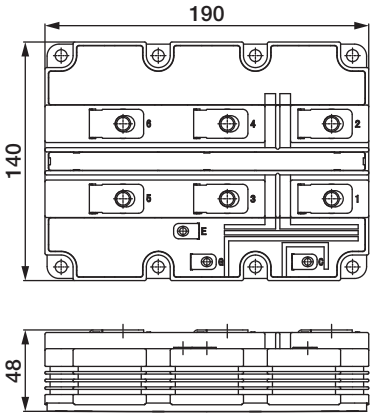
05

CM400HG-66H
CM200HG-130H



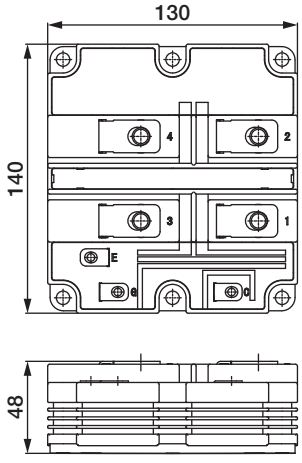
06

CM1800HG-66X, CM900HGB-90X
CM1350HG-90X, CM1500HG-90X
CM600HGB-130X, CM600E4G-130X
CM900HG-130X, CM1000HG-130XA
etc.



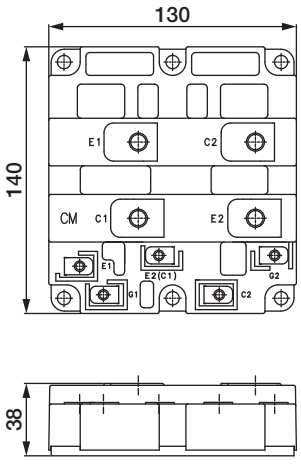
07

CM900, 1000HG-90X
CM800HG-90R
CM600HG-90H/130X
CM400HG-130H



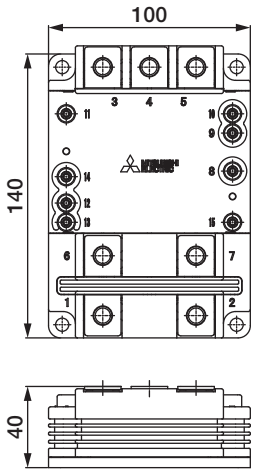
08

CM400DY-50H/66H



09

CM1200DA-34X
CM450DA-66X, CM600DA-66X

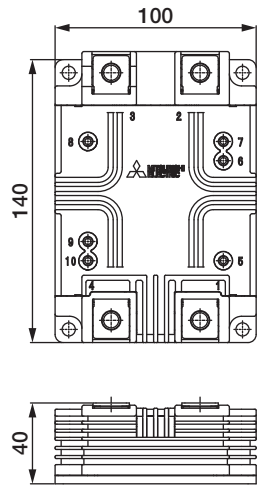


Outline Drawing of HVIGBT Modules

Unit:mm

10

CM450DE-66X, CM600DE-66X
CM450DE-90X, CM300DE-130X



HVDIODE Modules

Series , Main Application

Series	Main Application
HVDIODE Modules	Traction/Power transmission/Motion control

Data sheet here

Rated Lineup

		Rated current											
		200A	250A	300A	400A	450A	600A	800A	900A	1000A	1200A	1500A	1800A
Rated voltage	1700V										●		●
	3300V				●		●				●		
	4500V			●		●					●		
	6500V		●			●				●			

Series Matrix of HVDIODE Modules (No.: Number of outline drawing, see page 42)

V_{PRM} / I_F	1700V Connection	Type	No.	3300V Connection	Type	No.	4500V Connection	Type	No.	6500V Connection	Type	No.
200A										RM200DG-130S	D	G 13
250A										RM250DG-130F	D	G 13
300A							RM300DG-90S	D	G 13	RM300DG-130X**	D	G 13
400A				RM400DG-66S RM400DY-66S	D D	G 13 B 14	RM400DG-90F	D	G 13			
450A							RM450DG-90X	D	G 13	RM450DG-130X**	D	G 13
600A				RM600DY-66S RM600DC-66X	D D	B 14 C 14	RM600HE-90S	H	C 13	RM600DG-130S RM600DG-130X**	D D	G 13 G 13
800A							RM800DG-90F	D	G 13			
900A							RM900HC-90S RM900DB-90S RM900DG-90X**	H D D	C 14 B 14 G 13			
1000A				RM1000DC-66F	D	C 14				RM1000DG-130XA	D	G 13
1200A	RM1200DB-34S RM1200DC-34X**	D D	B 11 C 11	RM1200DG-66S RM1200HE-66S RM1200DB-66S RM1200DC-66X** RM1200DG-66X	D H D D D	G 13 C 12 B 14 C 14 G 13	RM1200DG-90F	D	G 13			
1500A				RM1500HE-66F RM1500DC-66F	H D	C 12 C 14	RM1500DC-90X** RM1500DG-90X**	D D	C 14 G 13			
1800A	RM1800HE-34S	H	C 12									
Connection	H  D 											

[Type]
B : Cu base plate 6kV Isolation C : AlSiC base plate 6kV Isolation
G : AlSiC base plate 10kV Isolation

★★: Under Development
The outline drawing is written the figure of principal part numbers that have a common dimension.

Evolution of HVDIODE Module Series

1.7kV: S Series → X Series

3.3kV / 4.5kV / 6.5kV: S Series → F Series → X Series

Type Name Definition of IGBT Modules

RM 1200 D G -66 X

- RM: CM: IGBT, RM: DIODE, PM: IPM
- 1200: Rating current
- D: Connection type
- G: Outline drawing and other specifications
- -66: Voltage class
- X: Series name

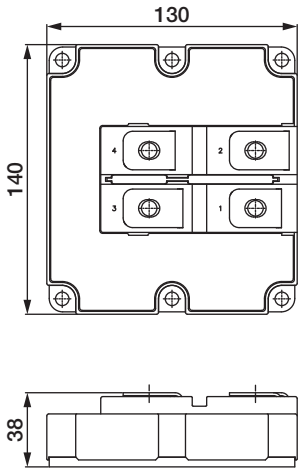
Lineup of HVDIODE Modules

Outline Drawing of HVDIODE Modules

Unit:mm

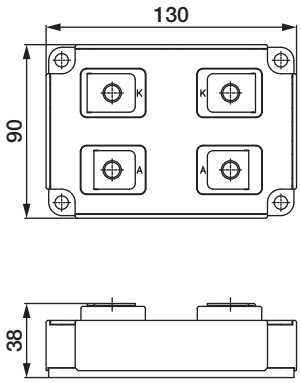
11

RM1200DC-34X
RM1200DB-34S



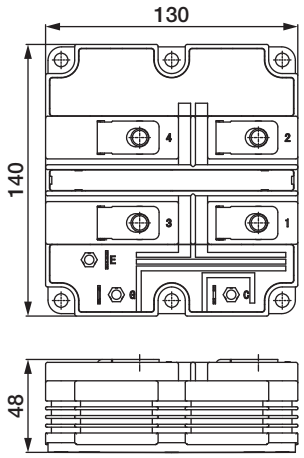
12

RM1800HE-34S, RM1500HE-66F
RM1200HE-66S, RM600HE-90S



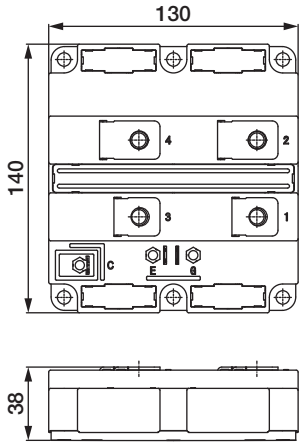
13

RM1200DG-66X
RM450/900/1500DG-90X
RM300/450/600DG-130X
RM1000DG-130XA
etc.



14

RM600/1200DC-66X
RM1500DC-90X
RM1000/1500DC-66F
RM400/600DY-66S
RM1200DB-66S, RM900DB/HC-90S



Lineup of MOSFET Modules

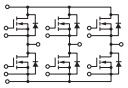
Series Matrix of MOSFET Modules

RoHS directive (2011/65/EU, (EU)2015/863) compliant

V_{DSS} / I_D	75V	Connection	100V	Connection	150V	Connection
100A	FM200TU-07A	T	FM200TU-2A	T	FM200TU-3A	T
200A	FM400TU-07A	T	FM400TU-2A	T	FM400TU-3A	T
300A	FM600TU-07A	T	FM600TU-2A	T	FM600TU-3A	T

Connection

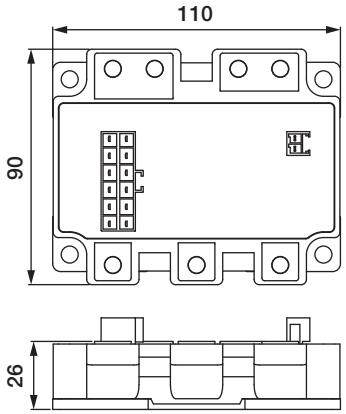
T



Outline Drawing of MOSFET Modules

Unit : mm

FM200TU-07A, -2A, -3A
FM400TU-07A, -2A, -3A
FM600TU-07A, -2A, -3A



Data sheet here

Power Modules for xEV

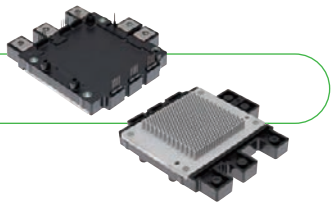
Series , Main Application

Series	Main Application
J1	xEV
J	

Rated Lineup

		Rated current		
		300A	600A	700A
Rated voltage	650V	▲	●	●

Featured Products



Package with 6-in-1 connection and integrated water-cooled fin contributes to more compact, high-power

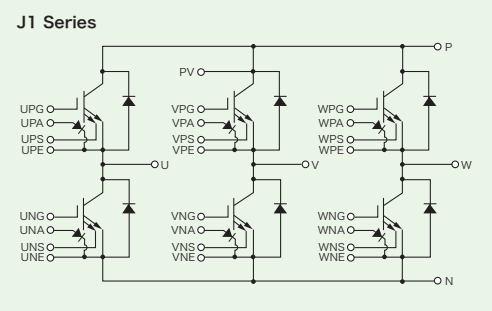
J1 Series power Modules for xEV

CT600C1A060-A, CT700CJ1A060-A

<Main Features>
- Integrated direct water-cooling structure with cooling fins and 6-in-1 connection contribute to more compact inverters for xEV
- Direct lead bonding (DLB) structure ensures high reliability
- Loss further reduced by incorporating 7th-generation IGBT built with a CSTBT™* structure
- On-chip current sensor that enables high-speed current-cutoff protection is installed
- Completely lead-free, confirms to RoHS directive (2011/65/EU)
- Suitable for a variety of electric and hybrid vehicle inverters

*CSTBT™: Mitsubishi Electric's unique IGBT that utillizes the carrier cumulative effect.

Block Diagram



Features

Common

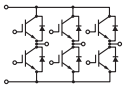
- Long power/temperature cycle life
- High-precision on-chip temperrature sensor
- High traceability in managing materials/components for each product throughout the entire production process
- Package structure compliant with the End-of-Life-Vehicles Directive, regulations relating to substances of enviromental concern

J Series T-PM (Transfer-molded Power Module)

- Structure incorporates transfer molding and original direct lead bonding(DLB) technique
- DLB structure reduces internal wiring resistance and inductance
- Completely Pb-free (including the pins)

Power Modules for xEV

Matrix of 650V Power Modules

V_{CES}	650V					
Series / I_C	J1 Series			J Series		
	Power Module with pin fin	Connection	No.	T-PM	Connection	No.
300A	–	–	–	CT300DJG060	D	02
600A	CT600CJ1A060-A	C	01	–	–	–
700A	CT700CJ1A060-A	C	01	–	–	–
Connection	C  D 					

Type Name Definition of Power Modules for xEV

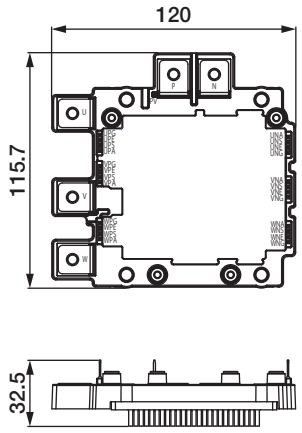
CT 600 C J1A 060

- Voltage class
- Series name and structure
- Connection type
- Rating current class
- CT: IGBT

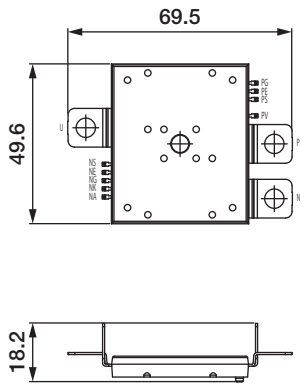
Outline Drawing of Power Modules for xEV

Unit:mm

01 **CT600CJ1A060-A**
CT700CJ1A060-A



02 **CT300DJG060**



MEMO

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